

# ILD related R&D Activities @ IFCA

Future Linear Collider Workshop, Sevilla, Feb. 10<sup>th</sup>



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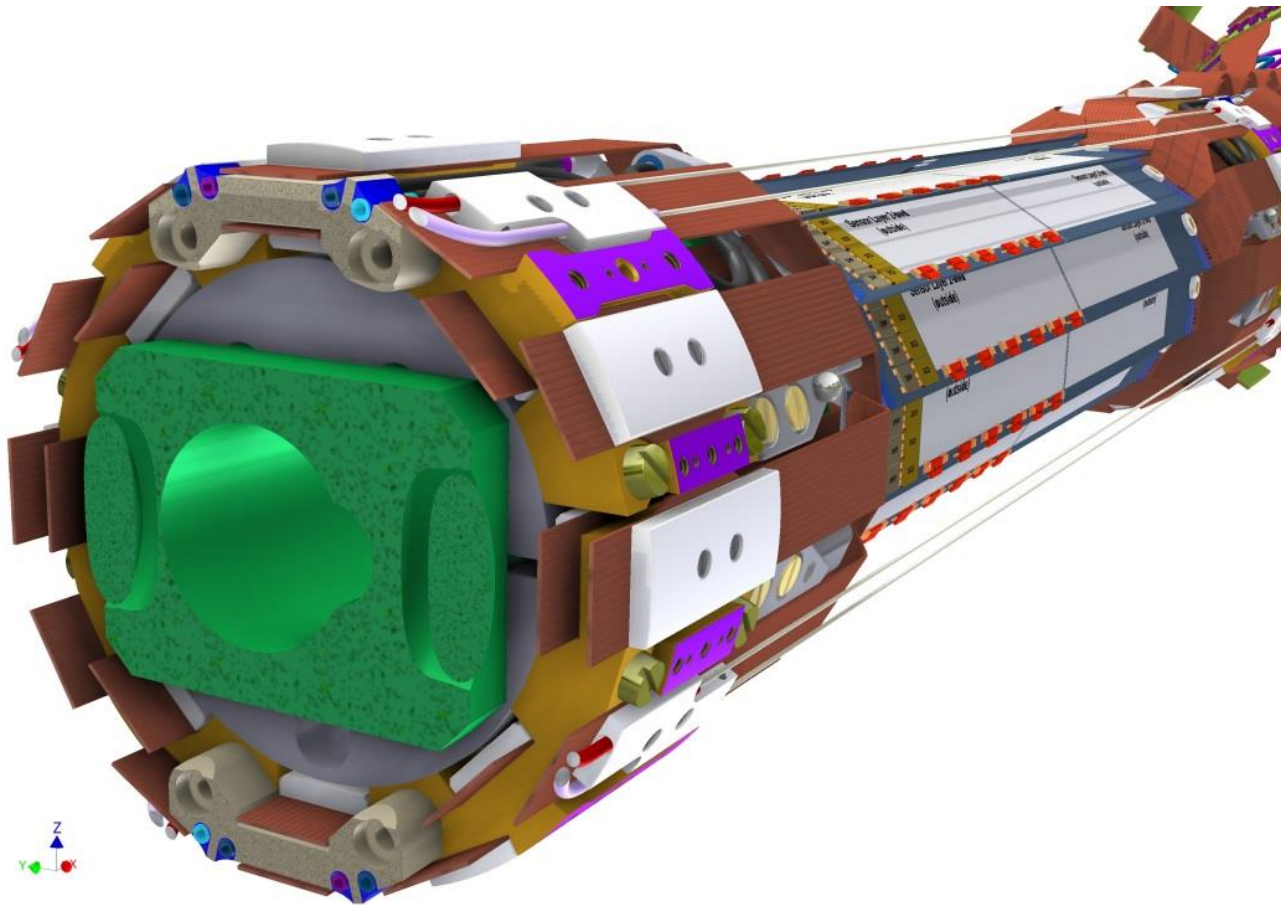


# Outline



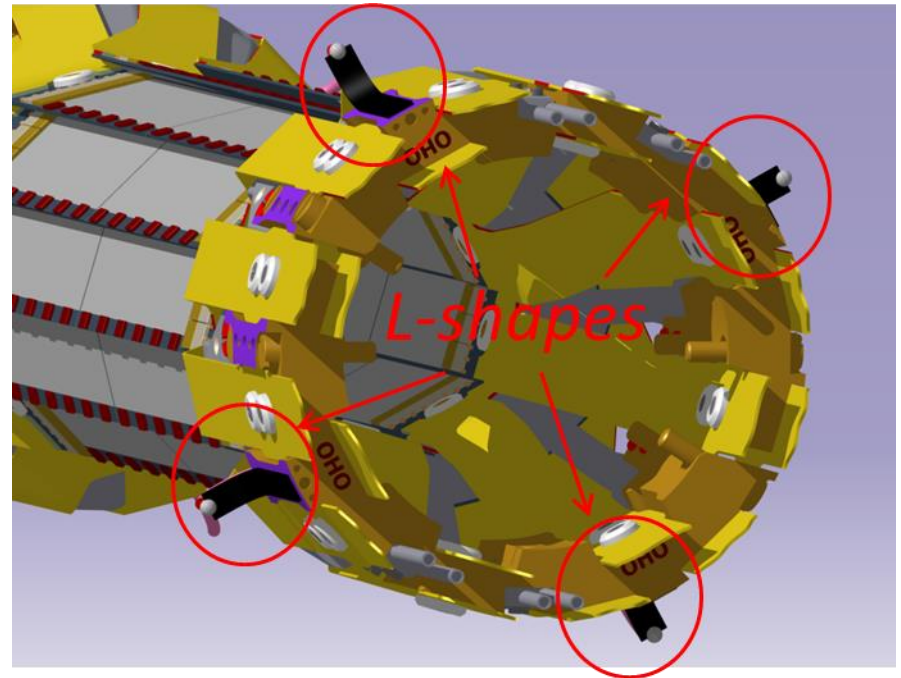
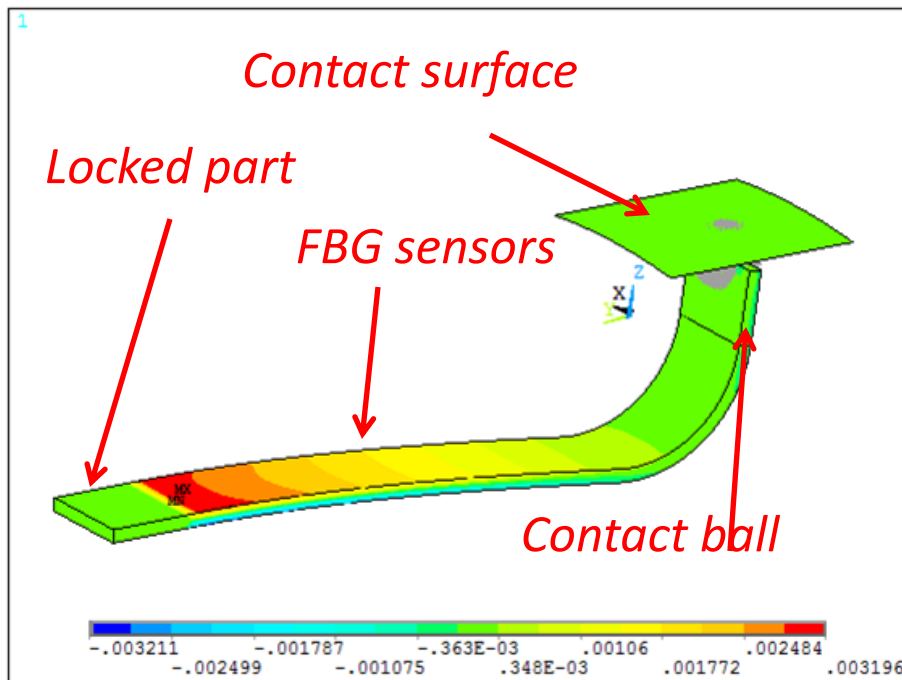
- A structural and environmental monitor for Belle-2 vertex detector based on Fiber Optic Sensor (FOS)
- R&D on microstrips sensors (resistive & low signal gain)

# FOS Monitor

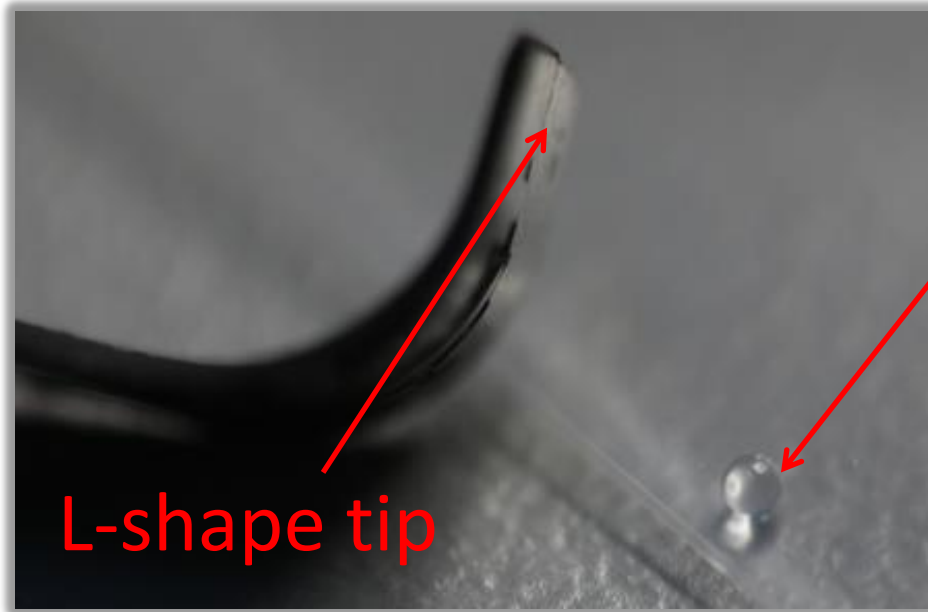


# L-shape basics

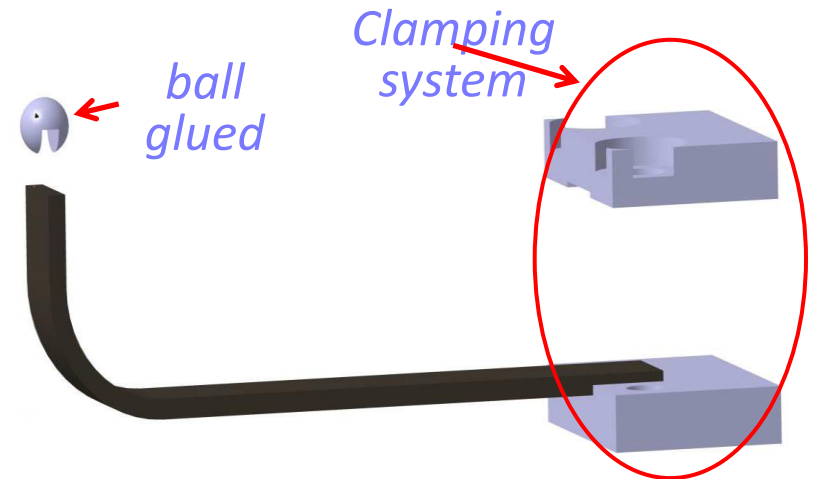
- Temperature & strain to displacement transducer with custom geometry for integration in PXD
- Readout speed from zero to 1KHz (vibrations)
- Currently three demonstrators manufactured



# L-Shape Demonstrators



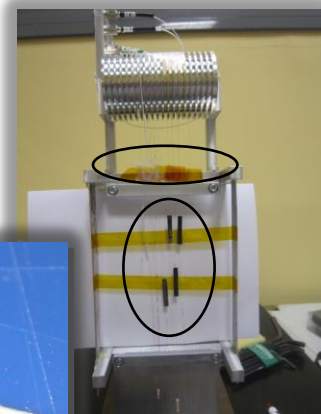
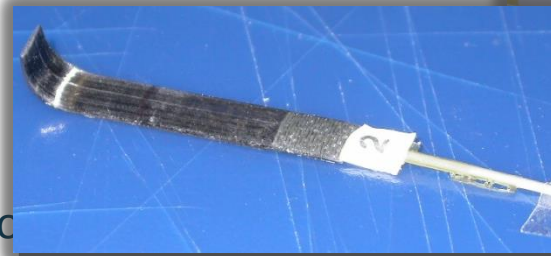
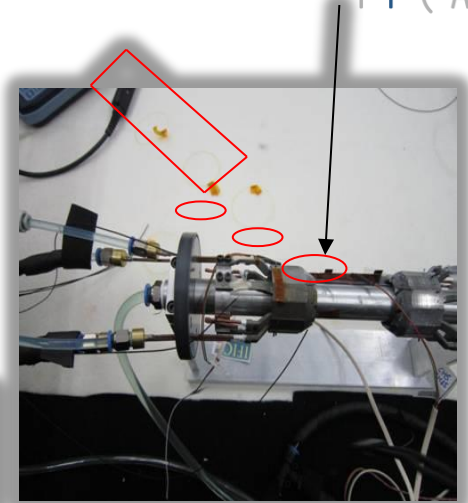
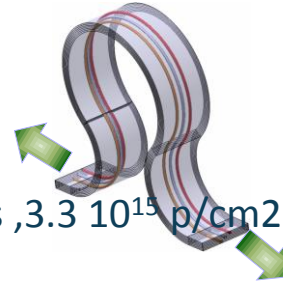
One millimeter Diameter Quartz contact ball



# FOS Monitor Timeline



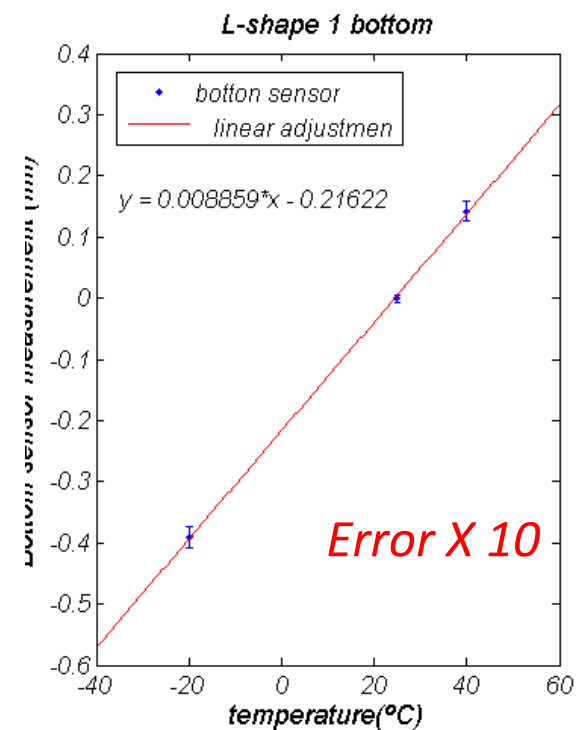
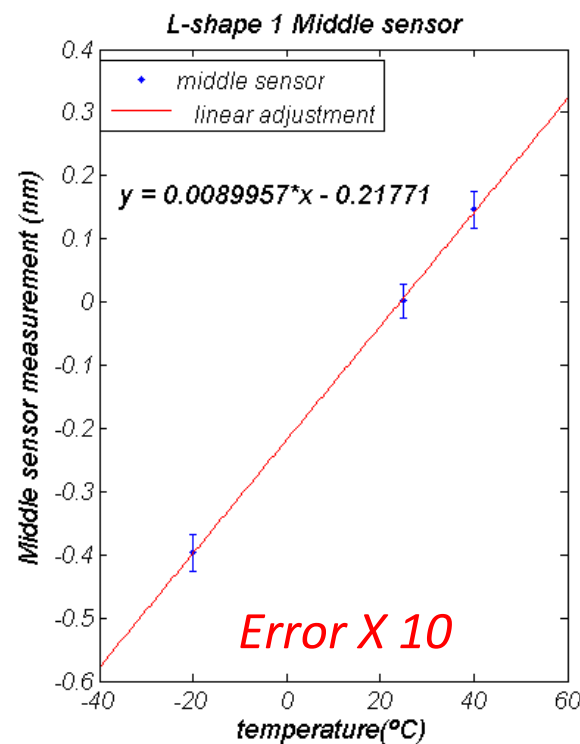
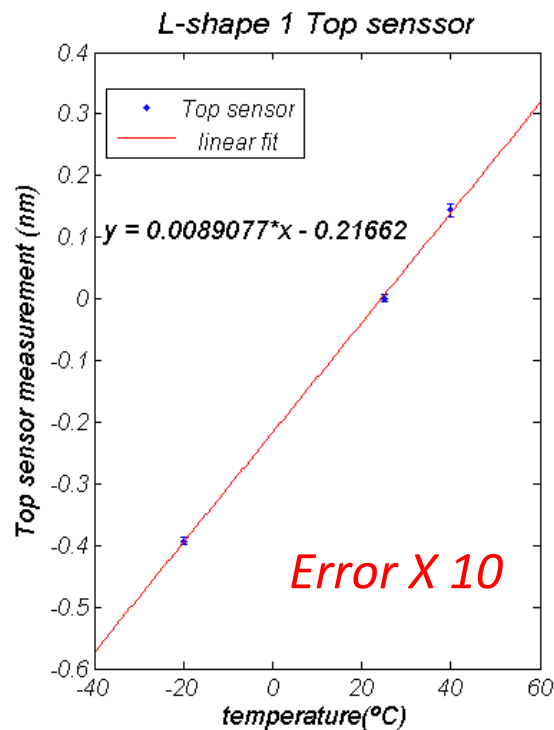
- ☑ 2009 Oct FOS Monitor proposal
- ☑ 2010 Jan Omega-shape proposal
- ☑ 2010 Oct. FOS radiation hardness study (1.5 GRads , $3.3 \cdot 10^{15}$  p/cm<sup>2</sup>)
- ☑ 2011 January First omega mechanical dummies
- ☑ 2011 Sept. FOS radiation hardness study ( 10 Mrads )
- ☑ 2011 Dec Proof-of-concept-prototype omega
- ☑ 2012 Feb Omega calibration.
- ☑ 2012 March New transducer design L-shape
- ☑ 2012 May Test in depfet mock-up at IFIC
- ☑ 2012 October L –shape calibration  
(resolution less 1 um ,accuracy $\approx$ 10 um )
- ☑ 2013 May Test in mock-up at IFIC (N<sub>2</sub> atmosphere)
- ✓ 2014 January commissioning at PXD-SVD commo





# Thermal calibrations & temperature compensation

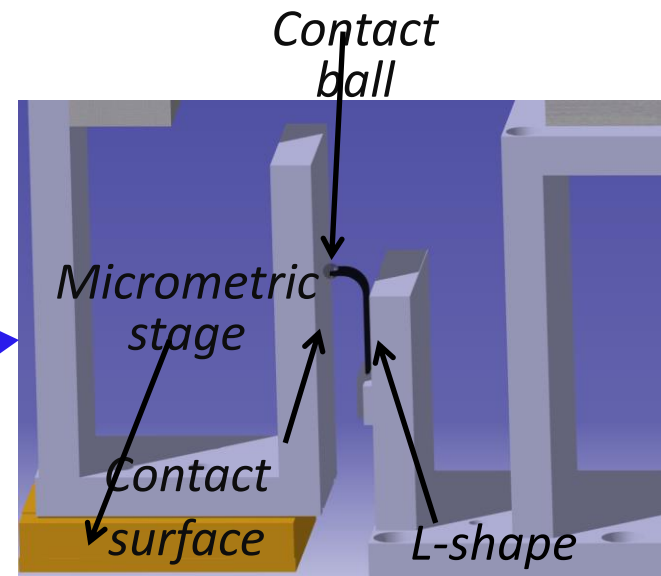
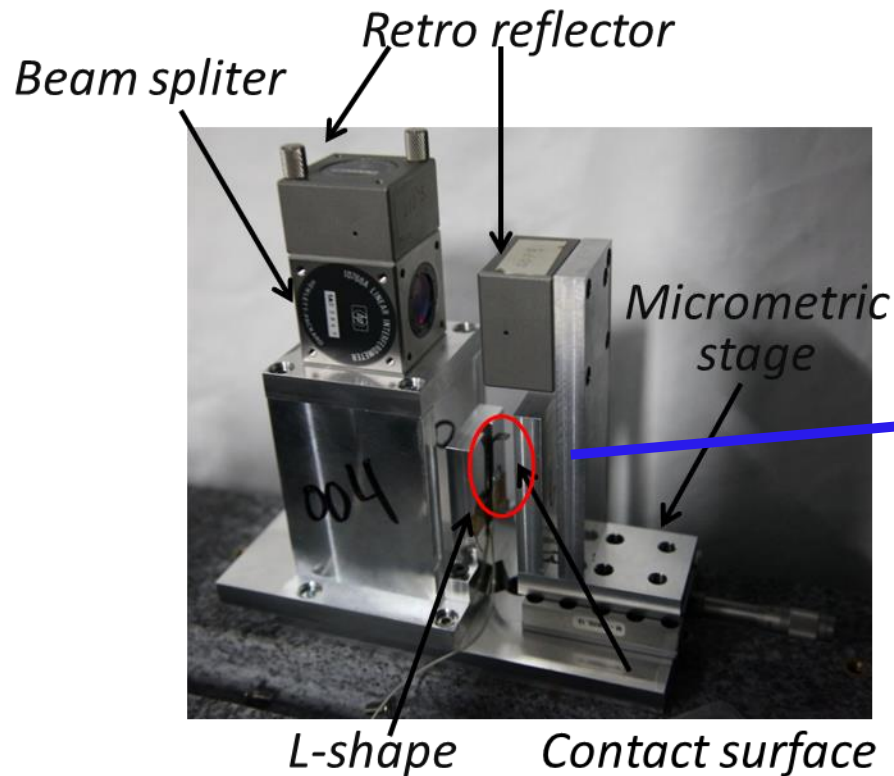
- Calibration using a SIKA thermocouples calibrator.
- The sensitivity of three sensors was constant and near the same (difference < 0.6%)  
*Maximum deviation < 3 pm (0.3 °C)*



- Trivial approach to temperature compensation

# Displacement Calibration

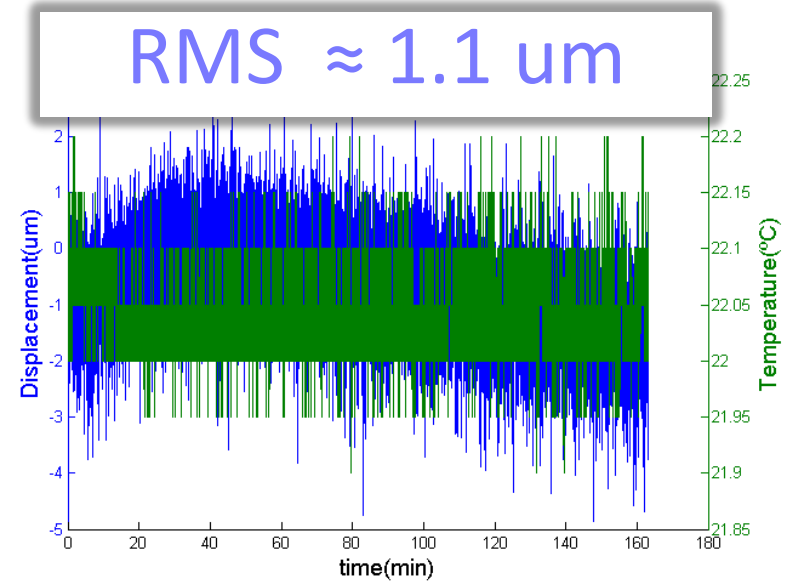
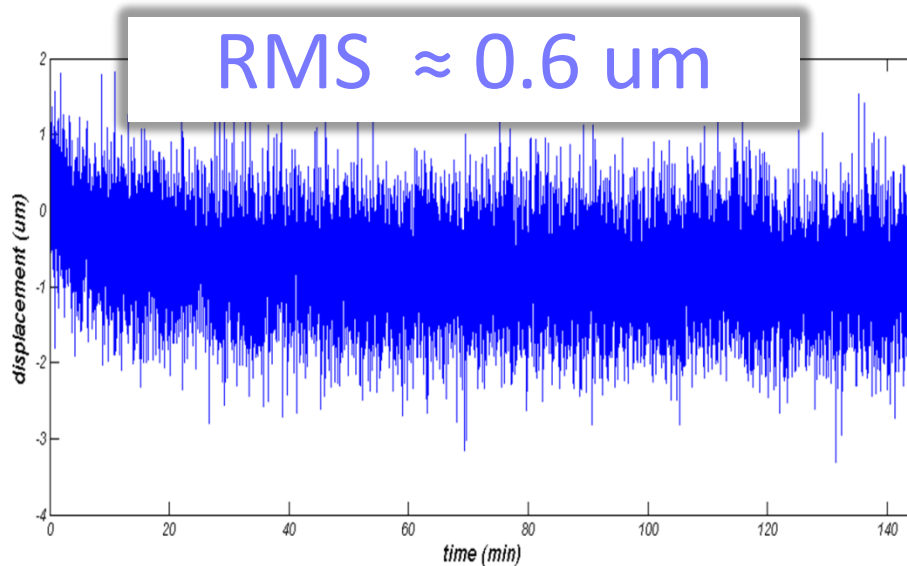
- Displacement measured with Michelson interferometer for high precision calibration (tenth of a micron)
- Readout of L-shape compared with true position (interferometer)





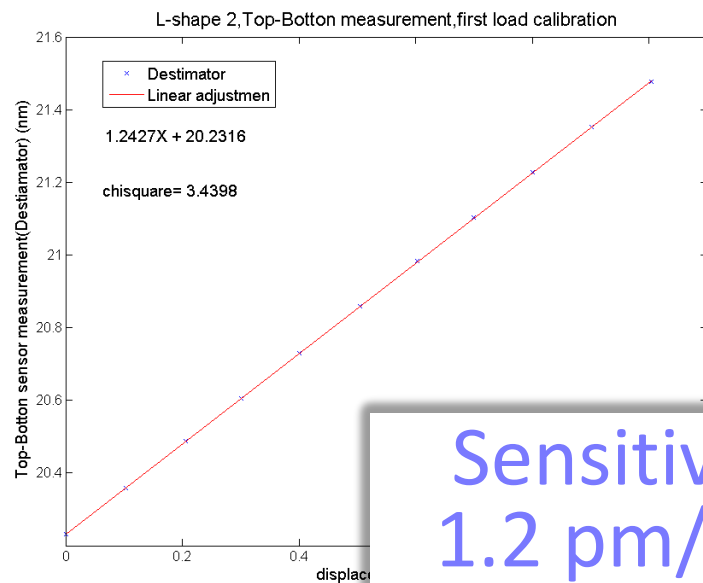
# L-shape Output Stability

- Short term studies (temperature constant  $\pm 0.1^\circ$  )
- Continuous readout of the sensor output.
- Stabilities below or about  $1\mu\text{m}$  (convolution with mechanics stability)

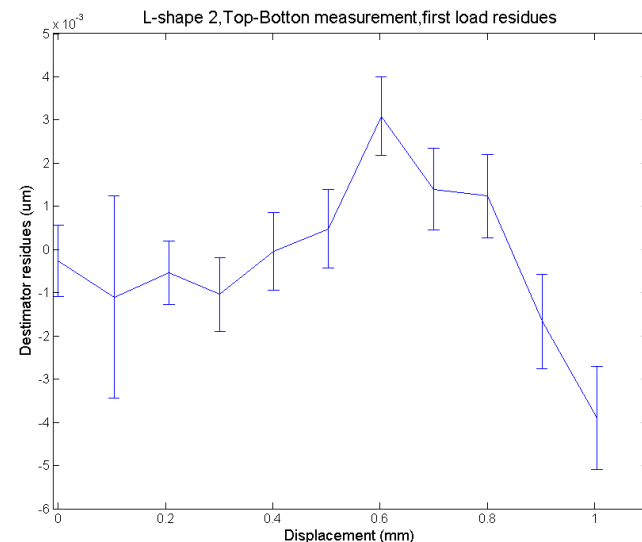


# L-shape Linearity vs. Displacement

- Calibration over a range of 1mm
- Resolution (readout resolution) 0.5  $\mu\text{m}$ .
- Accuracy (diff. Between inter & L-shape)  $\approx 2 \mu\text{m}$

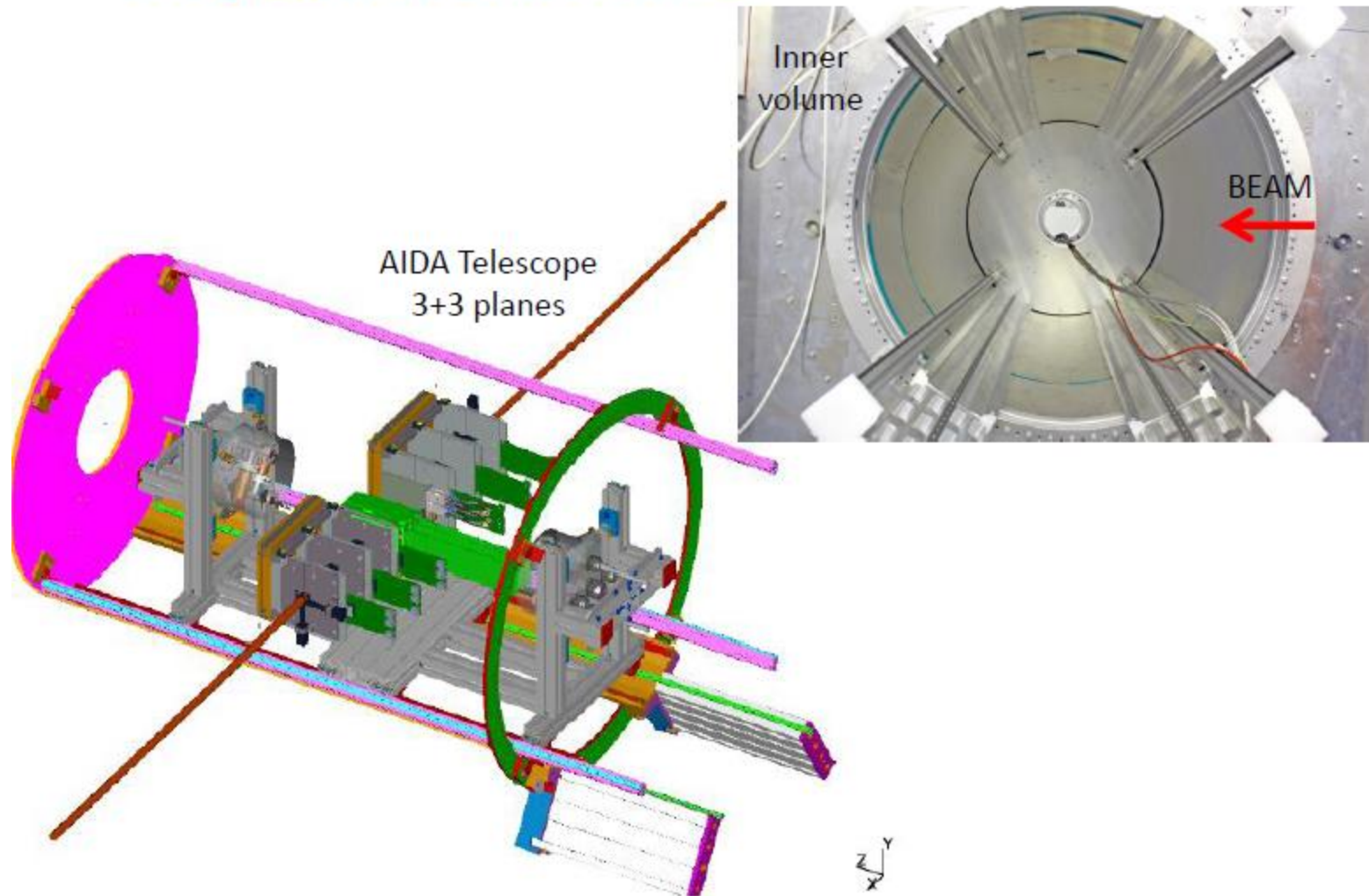


Sensitivity  
1.2 pm/ $\mu\text{m}$

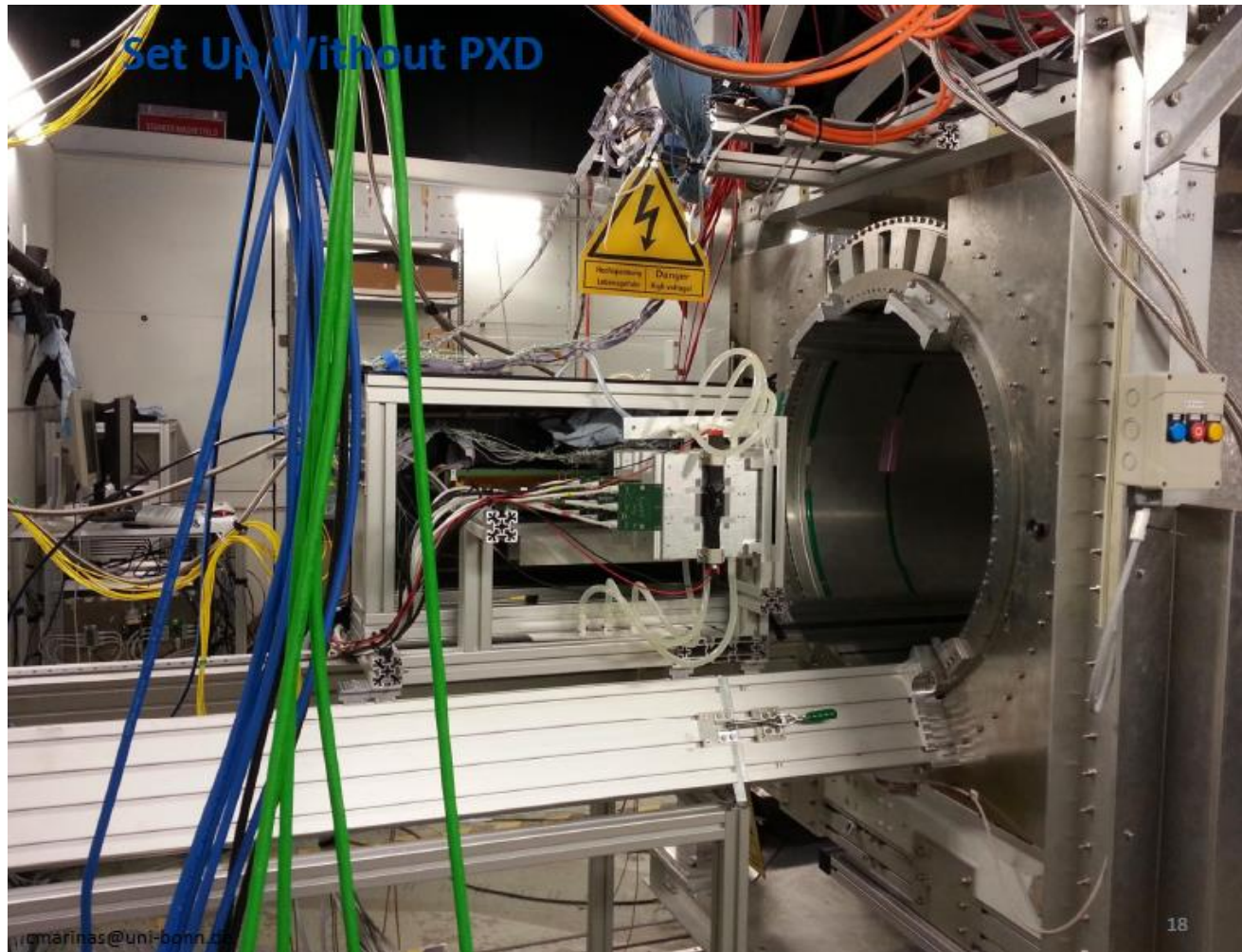


# PXD – SVD Integrated test beam

## Integration into the PCMAG

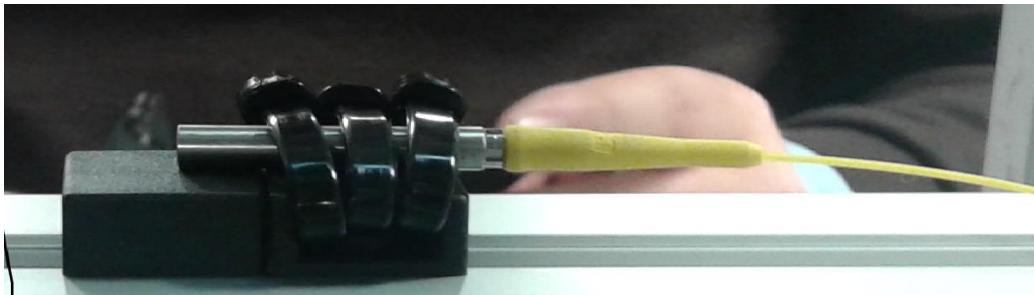
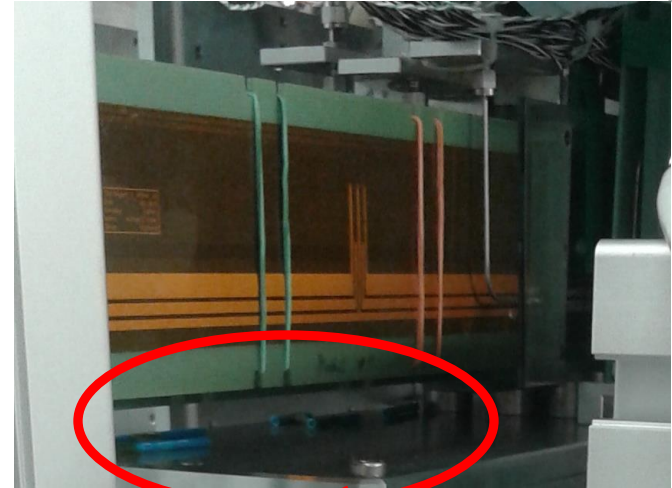


# PXD – SVD Integrated test beam





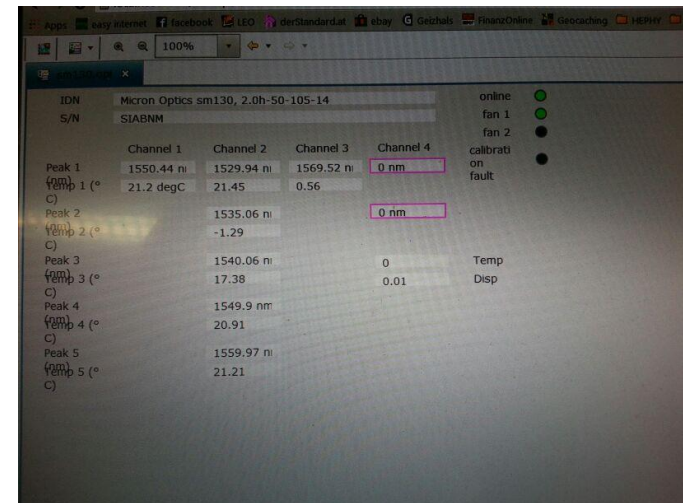
# FOS Monitor: FOS Packing



# FOS Monitor: DAQ – SC integration



- Optical routing of the sensors up to the interrogating units
- Readout integrated in EPICS (dedicated driver over Ethernet ). The integration went very smooth ready since the January 6<sup>th</sup>

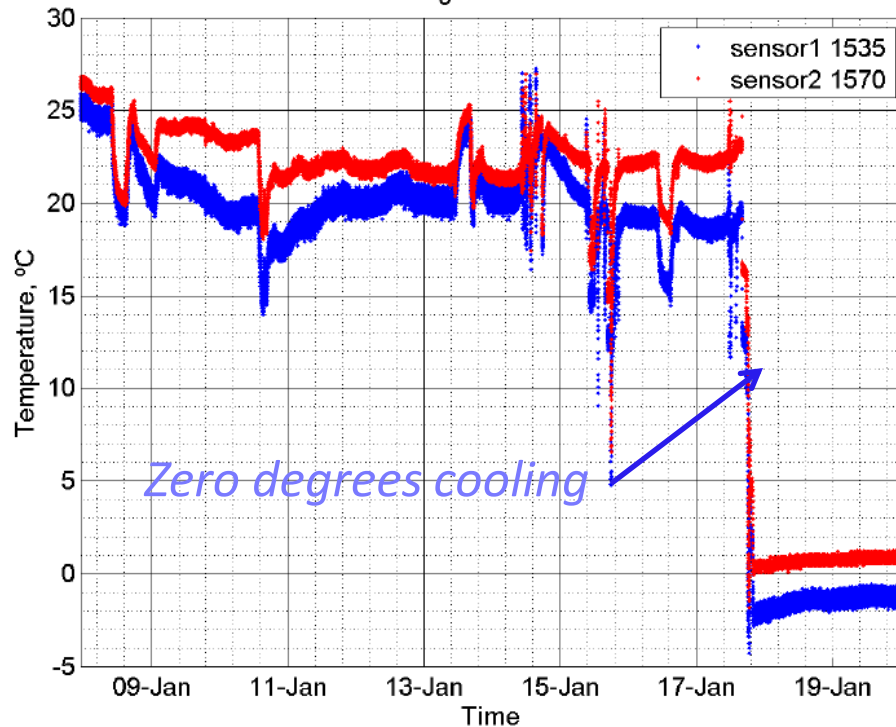




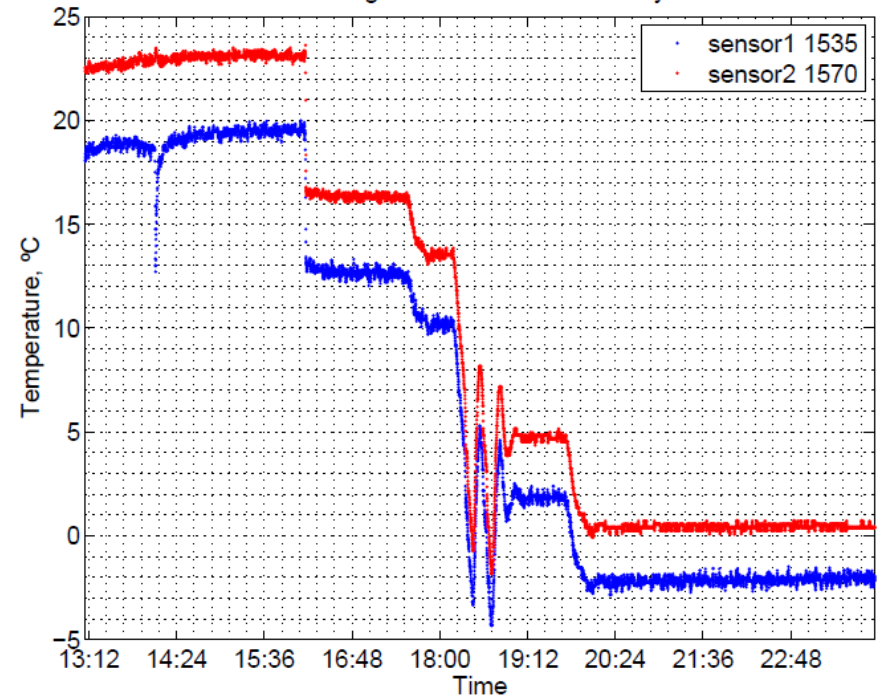
# FOS Monitor: Data: MARCO in-let & out-let lines



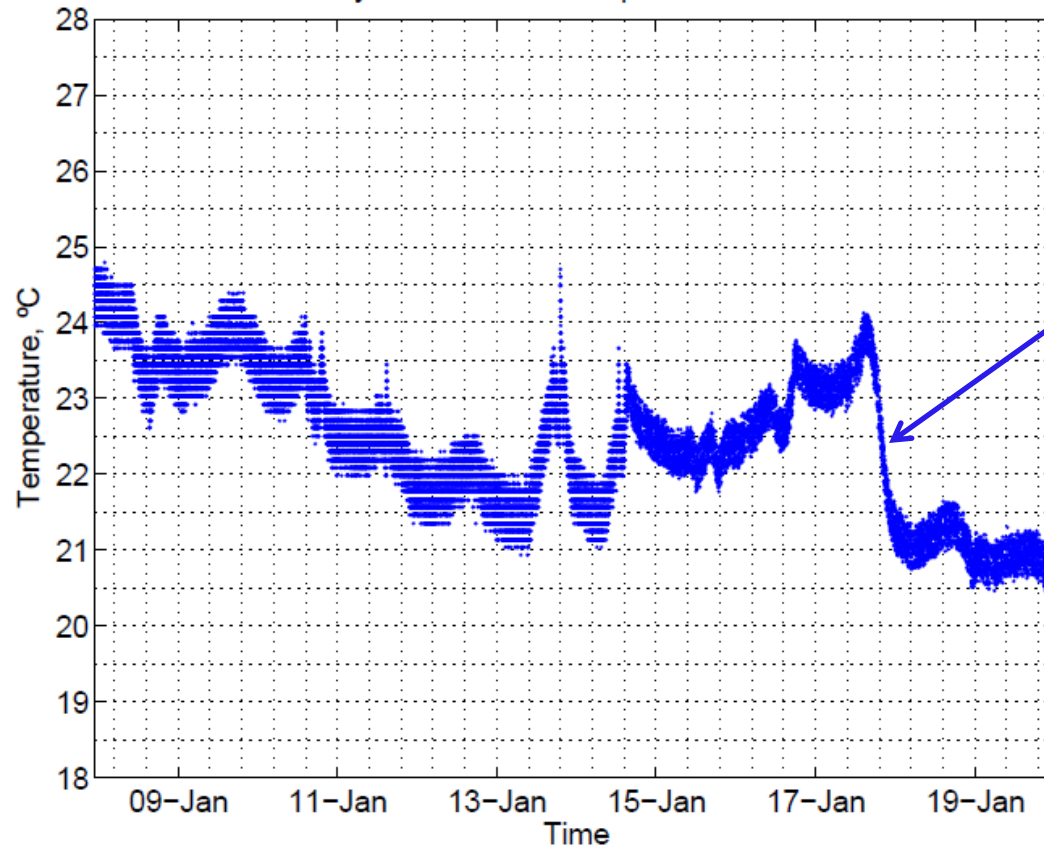
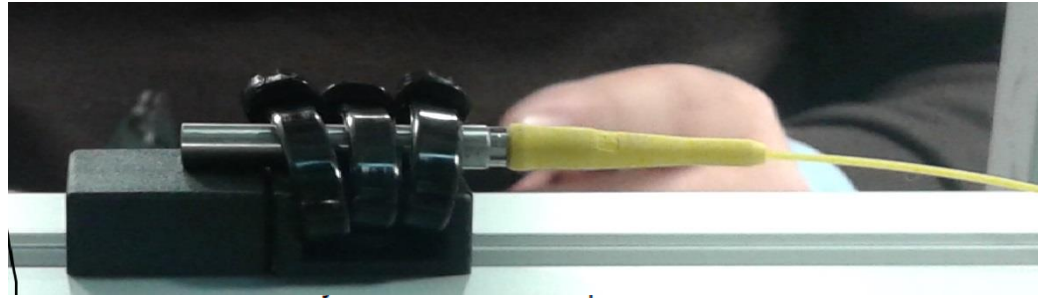
Cooling block sensors



Cooling block sensors 17 January

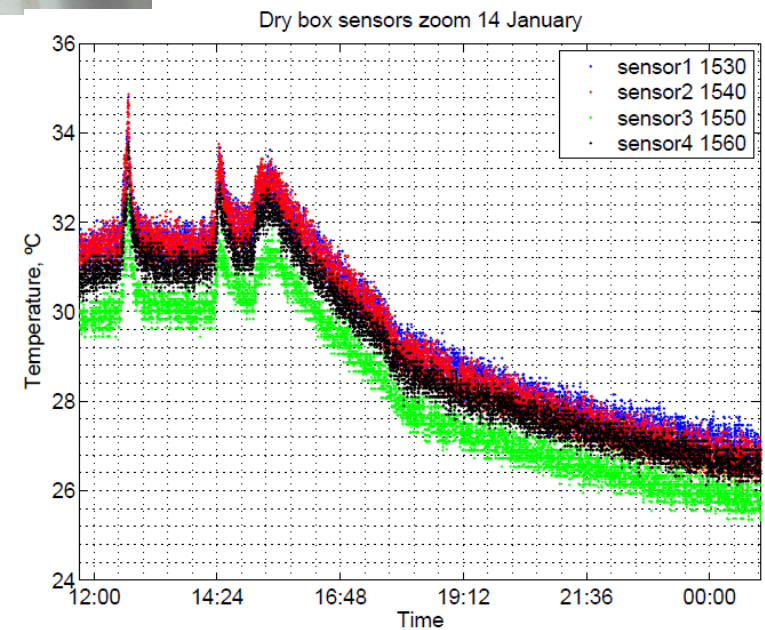
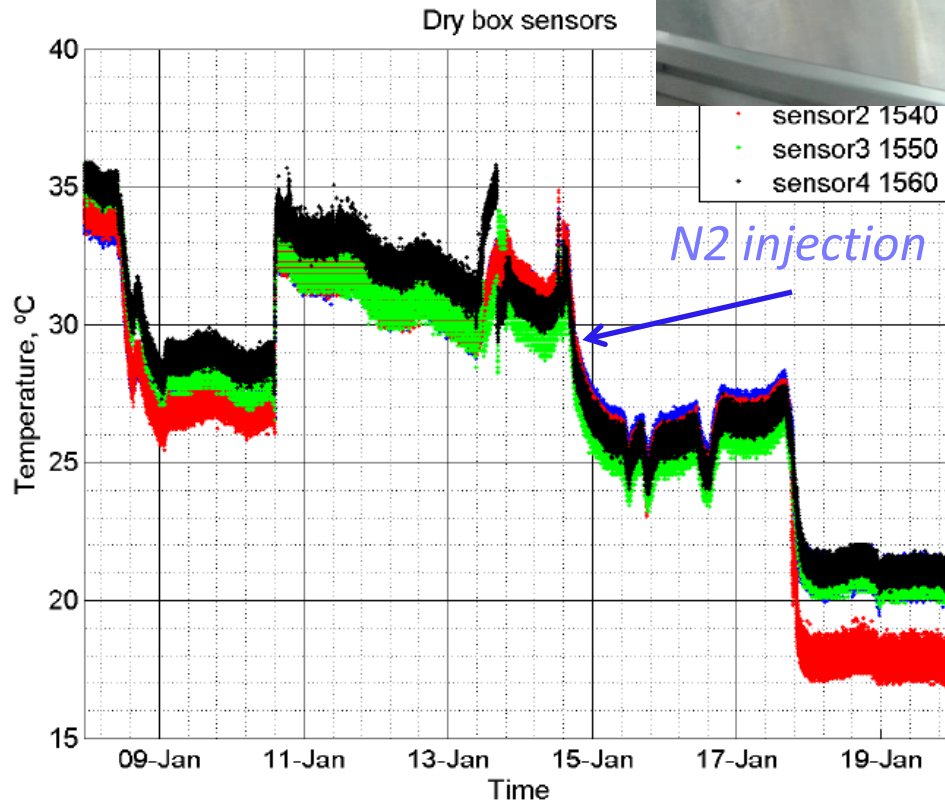
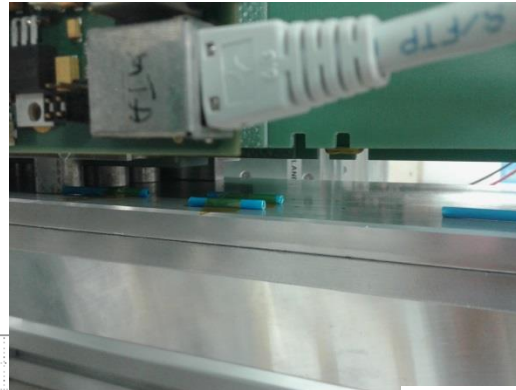


# FOS Monitor Data: Ambient Temp



*Zero degrees cooling*

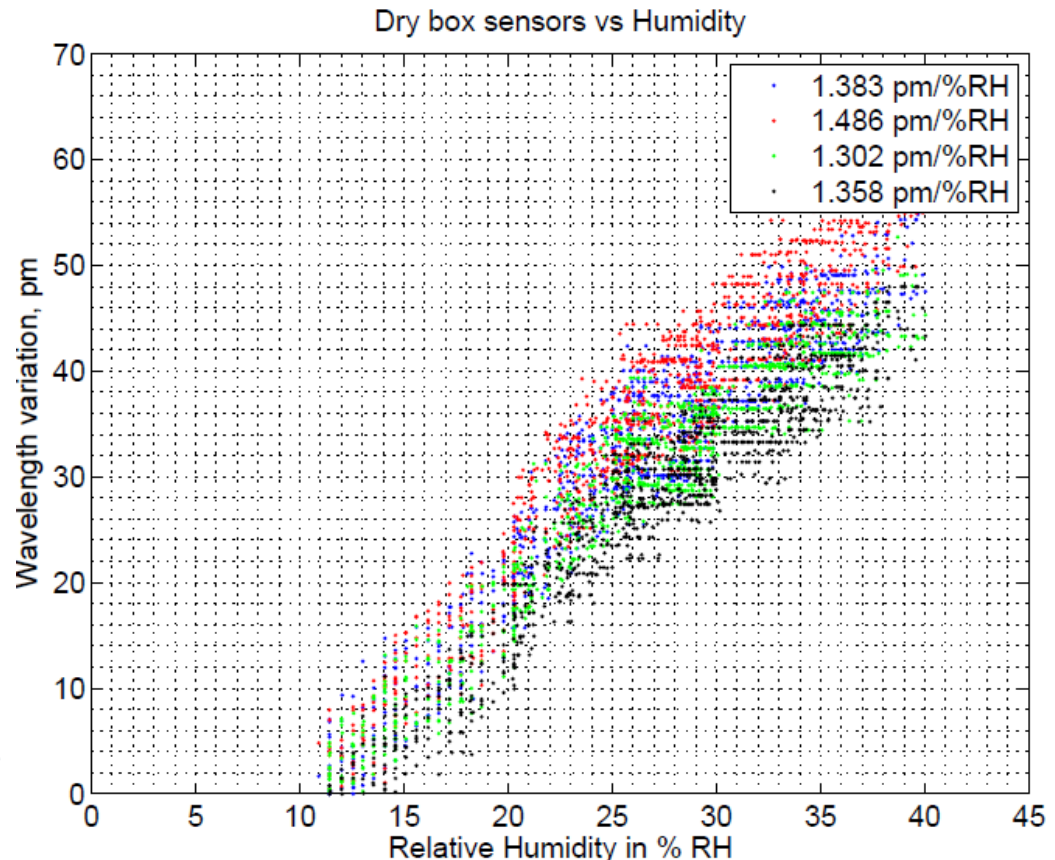
# FOS Monitor: Ambient Temp+%RH



# FOS Monitor: Humidity measurements



- Comparing the wavelength shift of ambient sensors (naked fibers) vs. commercial Humidity sensors inside the dry box.
- Excellent linearity and sensibility after temperature compensation



# Conclusions



- A FOS-based temperature and humidity monitor read-out through EPICS commissioned and running smoothly since the beginning of the test beam.
- Most of the R&D activities required for the implementation of FOS monitor (environmental and displacement) are completed. Still some more “academic “ loose ends to be completed this year.
- Next: System-wise activities for mechanical integration in Belle-II.

- Microstrip sensors with resistive electrodes.
- Low Gain Microstrip Sensors.



- Charge division in microstrips:
  - Long microstrips ladders (several tens of centimeters) proposed for the ILC tracking detectors.
  - Getting the particle hit coordinate along the strip using the charge division method.
  - Avoid the complexity of double sided sensors and the additional material of a second layer of sensors.
- Low gain segmented p-type pixels (strips)
  - Implementing a small gain in the segmented diode so we can reduce the thickness of the sensors without reducing the signal amplitude
  - Smaller contribution to the material budget.

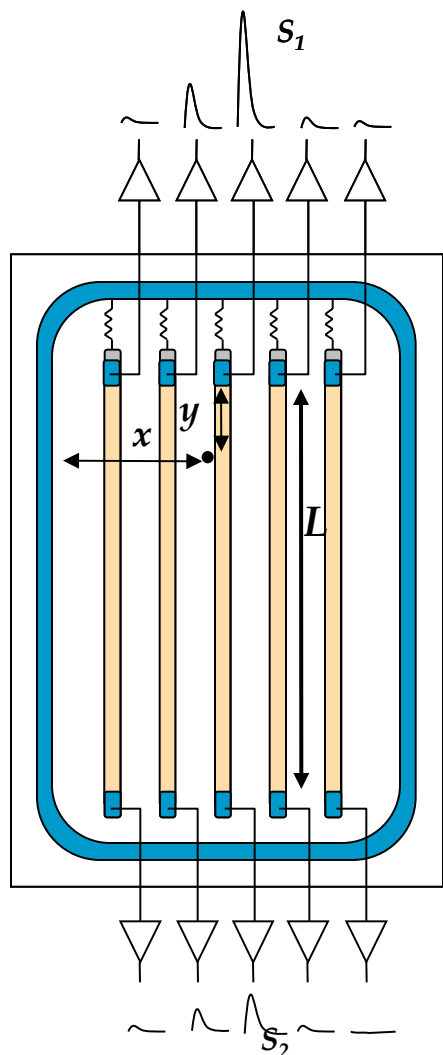
# Charge Division in uStrips

*Simple single-side AC-coupled microstrip detectors*

*with resistive coupling electrodes.*

*X-coordinate: cluster-finding algorithms for strip detectors.*

*Y-coordinate: Resistive charge division method.*



Resistive material  
Aluminium

**\*\* Electrode resistance  $\gg$  preamplifier impedance.**

$$S_1 = f(y)$$

$$S_2 = f(L-y)$$

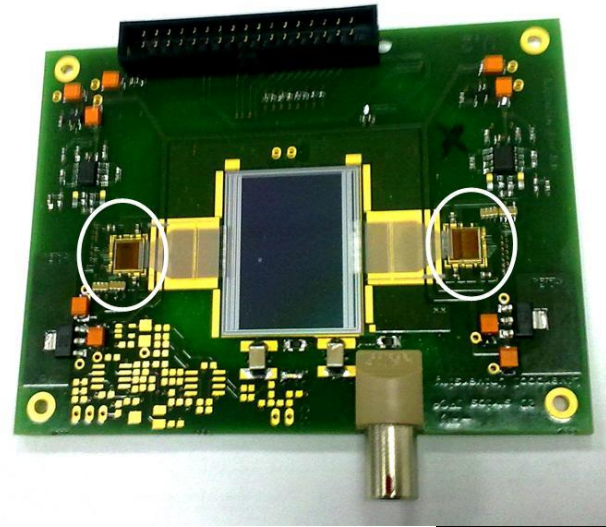
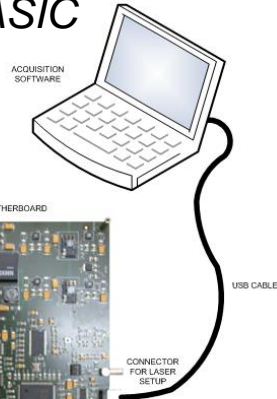
$$\frac{y}{L} = \frac{A_2}{A_1 + A_2}$$

**Resistive material: high doped polysilicon**

**\*\* V. Radeka, IEEE Transaction on Nuclear Science NS-21 (1974) 51**

# Proof-of-Concept Prototype

ALIBAVA DAQ system for  
microstrip detectors, based on  
the *Beetle* analogue  
readout ASIC



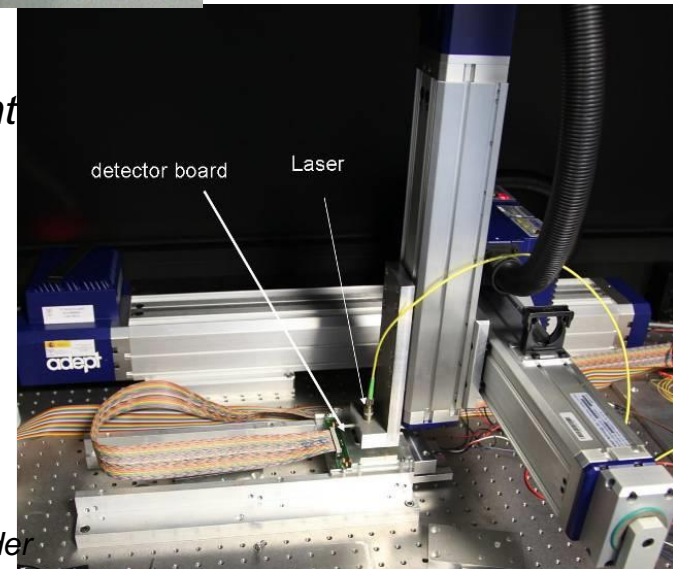
Strip:  
length = 20 mm  
width = 20  $\mu\text{m}$   
Pitches:  
Implant = 80  $\mu\text{m}$   
readout = 80  $\mu\text{m}$   
Electrode:  
 $R/\mu\text{m} = 2.8 \text{ Ohms}/\mu\text{m}$   
 $R/\mu\text{m} = 12.2 \text{ Ohms}/\mu\text{m}$

3D axis stage with displacement  
accuracy  $\approx 10 \mu\text{m}$

Pulsed DFB laser  
 $\lambda = 1060 \text{ nm}$

- Gaussian beam spot width  $\approx 15 \mu\text{m}$
- pulse duration 2 ns

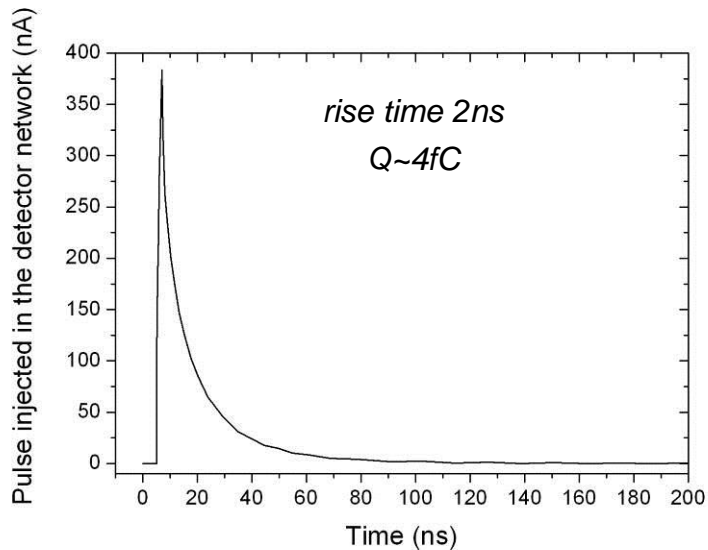
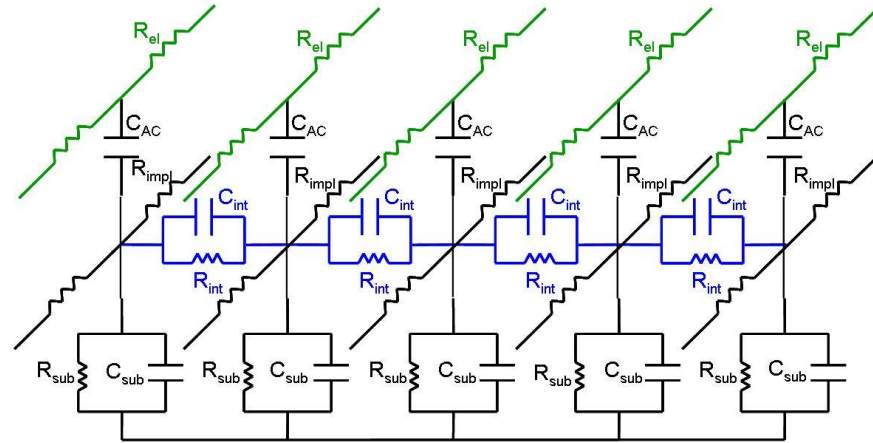
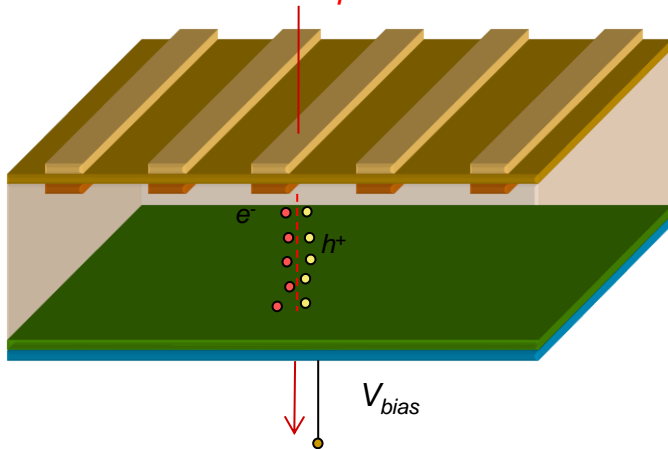
- 256 channels
- peaking time = 25 ns
- $S/N \approx 20$  for standard no irradiated detectors



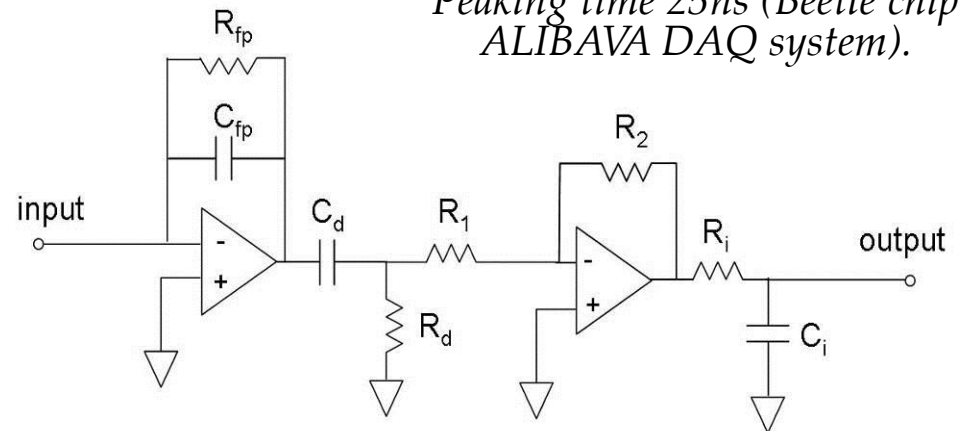
Clean room laboratory at IFCA, Santander

# Equivalent Electrical Circuit

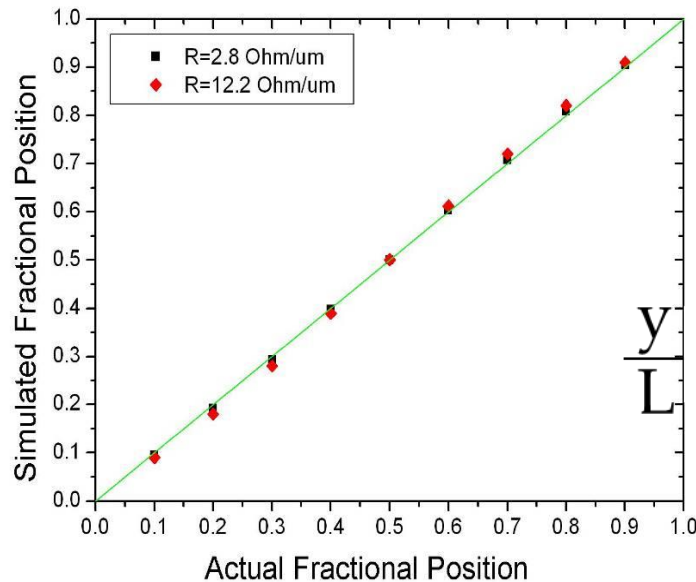
Detector ( $p^+$ -on- $n$ ) model \*\*\*  
80 cells 250  $\mu\text{m}$  long



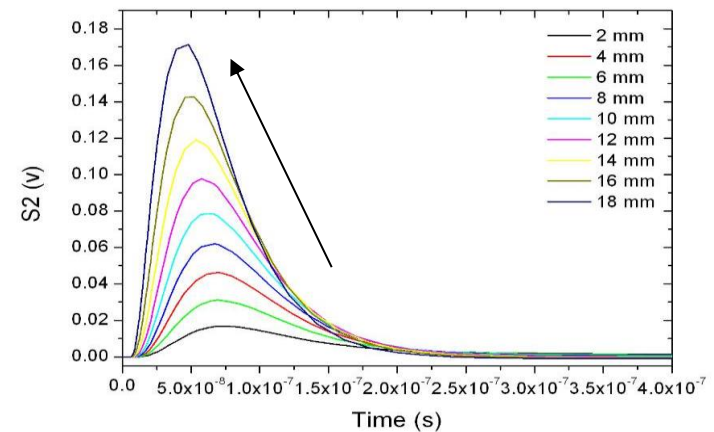
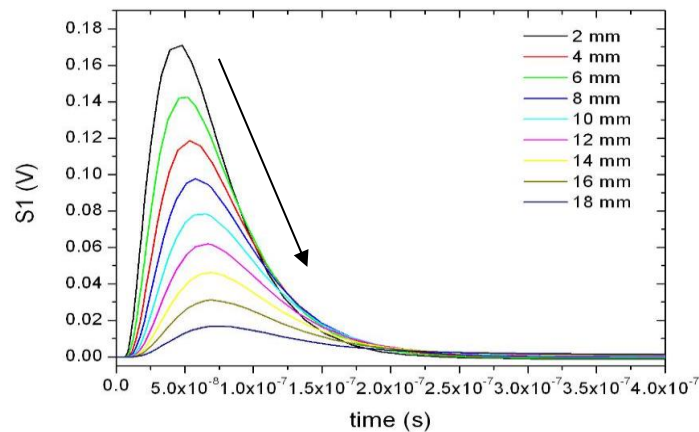
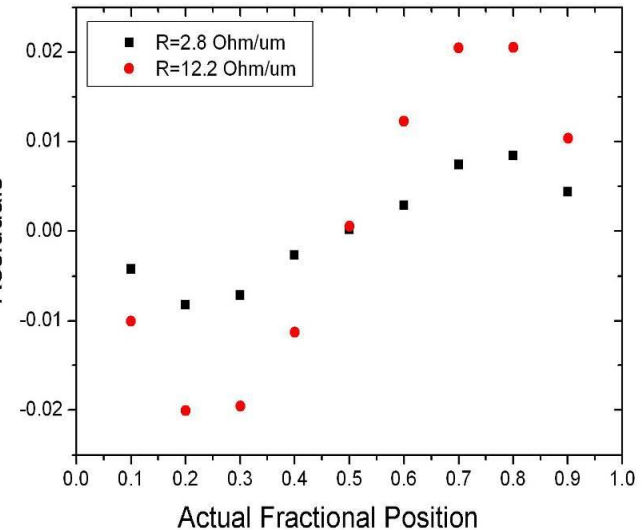
Peaking time 25ns (Beetle chip  
ALIBAVA DAQ system).



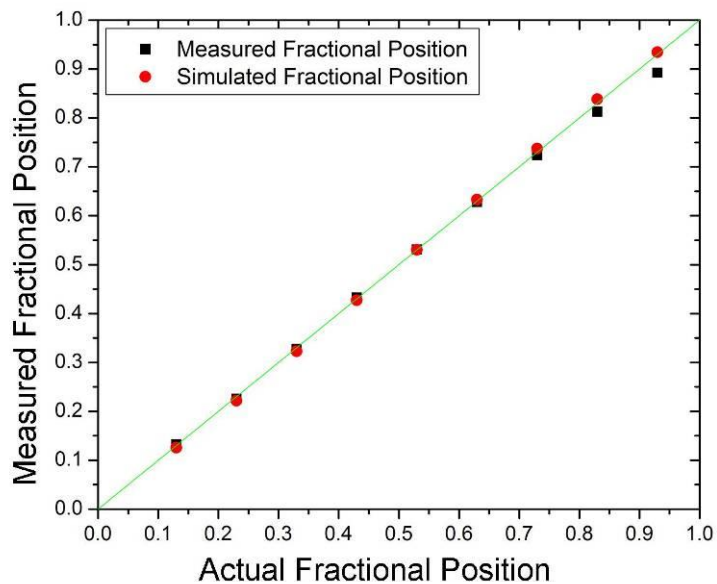
# Signal Propagation – Linearity (Simulation)



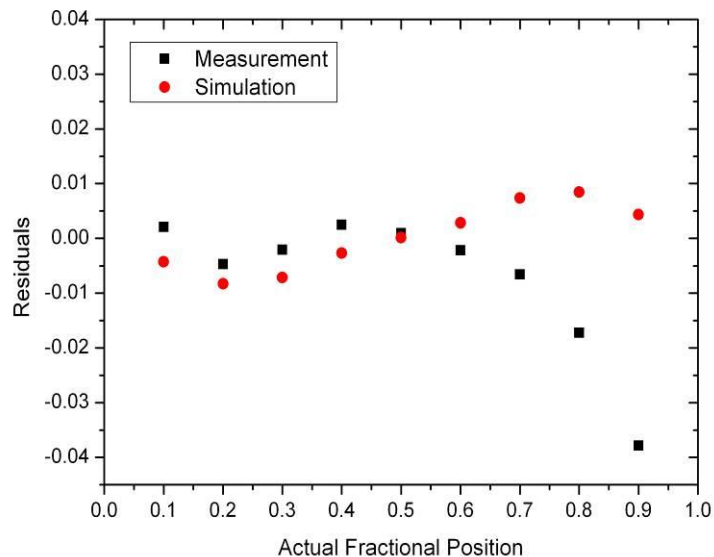
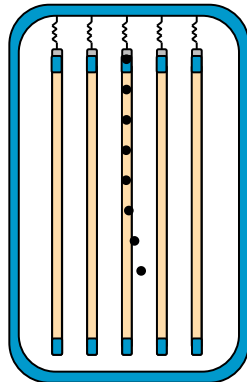
$$\frac{y}{L} = \frac{A_2}{A_1 + A_2} \text{Residuals}$$



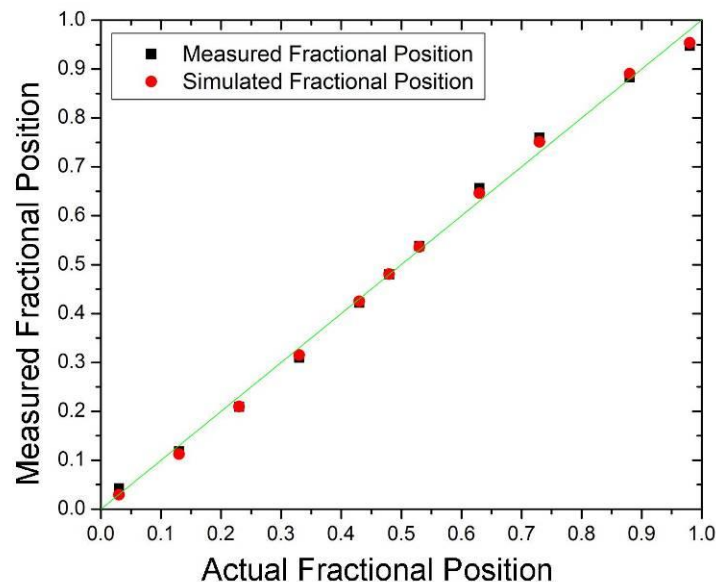
$R/l=2.8 \Omega/\mu m$



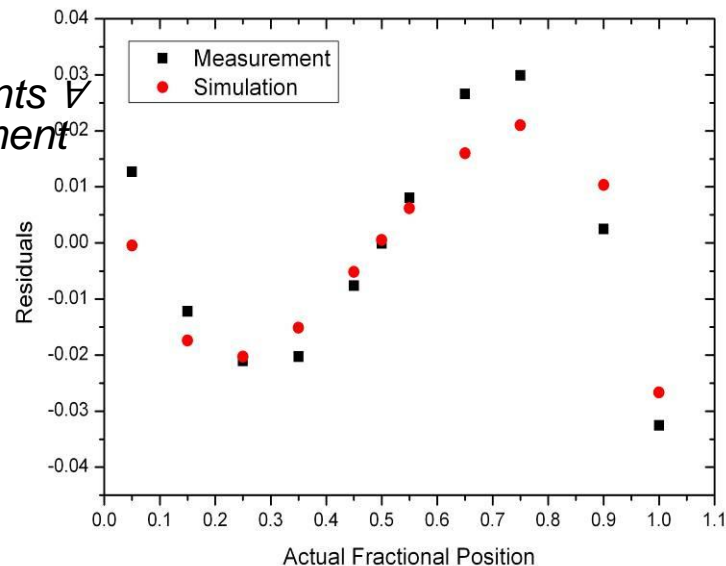
$$\frac{y}{L} = \frac{A_2}{A_1 + A_2}$$



$R/l=12.2 \Omega/\mu m$



20000 events  $\nabla$  measurement





# Longitudinal spatial resolution for 6 MIPs signal

$$\frac{A_2}{A_1 + A_2}$$

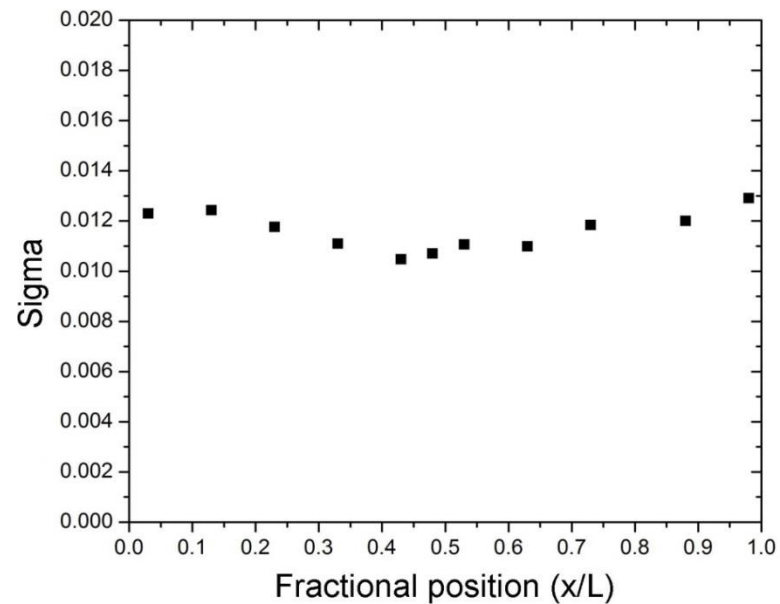
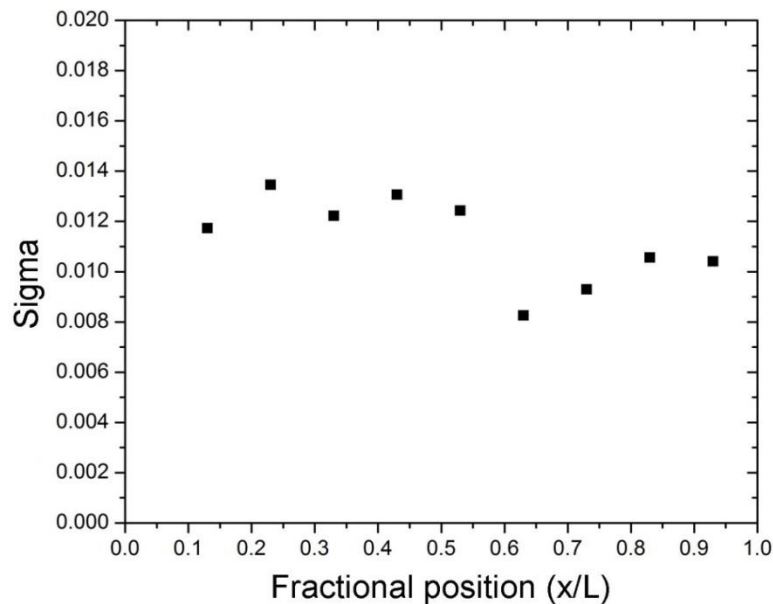
$$\sigma = \frac{A_1 A_2}{(A_1 + A_2)^2} \sqrt{\left(\frac{\sigma_{A_1}}{A_1}\right)^2 + \left(\frac{\sigma_{A_2}}{A_2}\right)^2 - 2\rho \left(\frac{\sigma_{A_1}}{A_1} \frac{\sigma_{A_2}}{A_2}\right)},$$

1.1%  $L \Rightarrow 220 \mu\text{m}$

$R/l = 2.8 \Omega/\mu\text{m}$

1.2%  $L \Rightarrow 240 \mu\text{m}$

$R/l = 12.2 \Omega/\mu\text{m}$



# Test Beam Characterization



*Test beam at CERN SPS Pion Beam, Nov 2012*

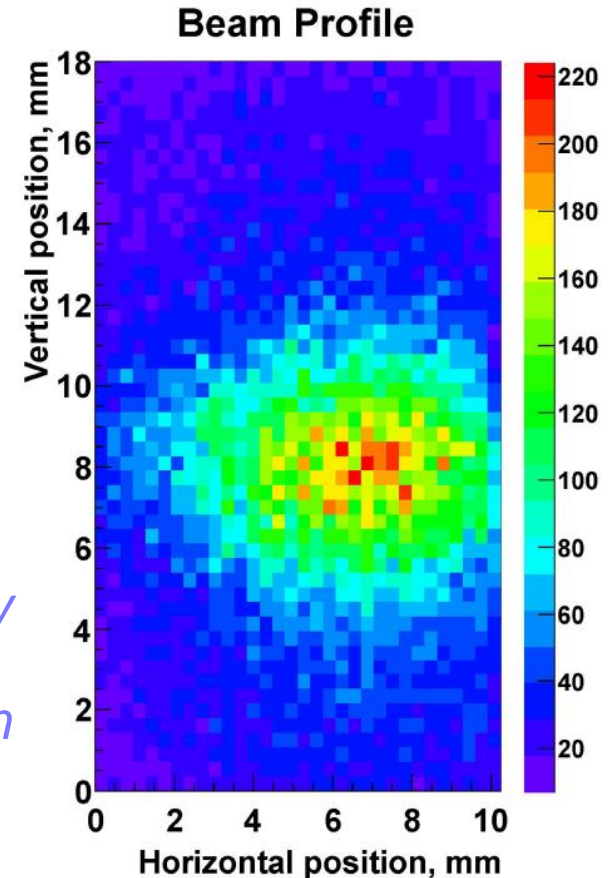
*First successful integration and synchronization with AIDA MIMOSA pixel telescope*

*Preliminary results:*

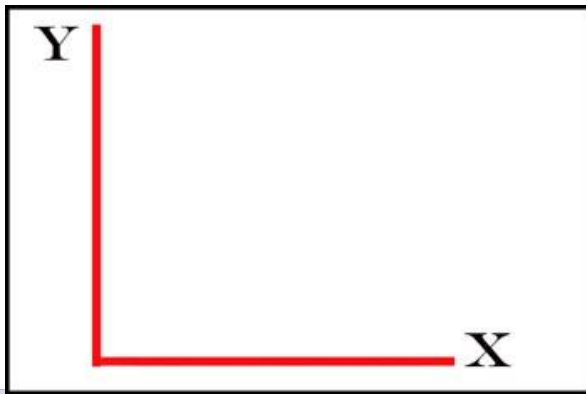
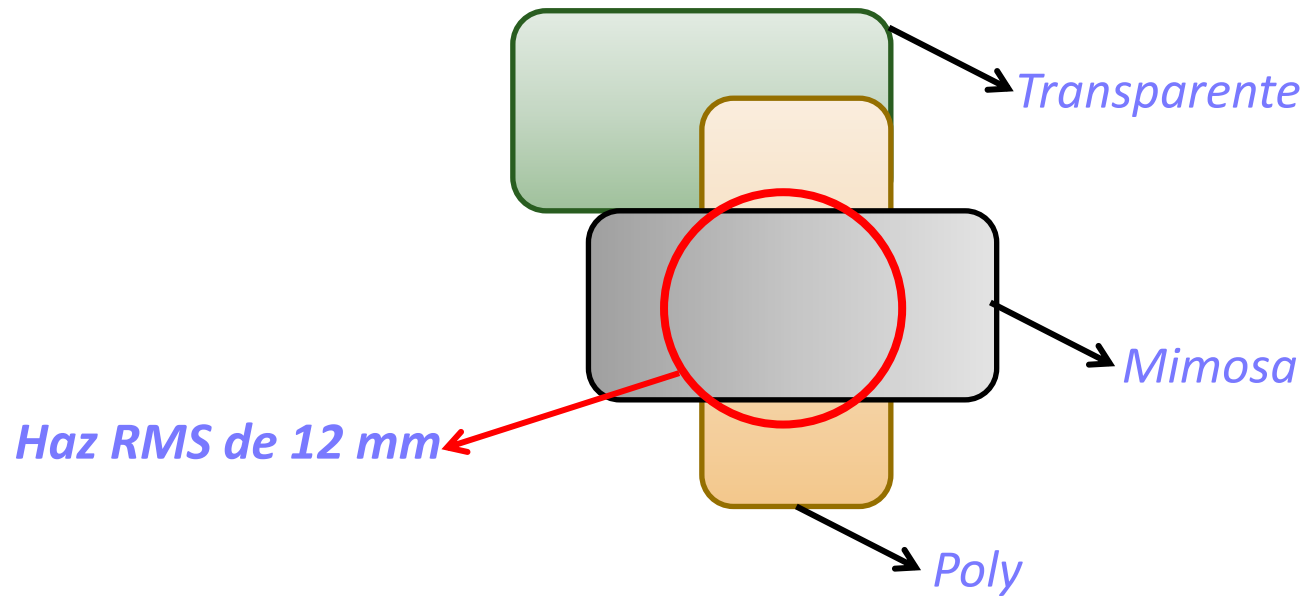
*Monitoring of beam profile.*

*Currently in progress:*

*Efficiency and resolution using tracking information.*



*Vista frontal del setup a escala (aproximada)*



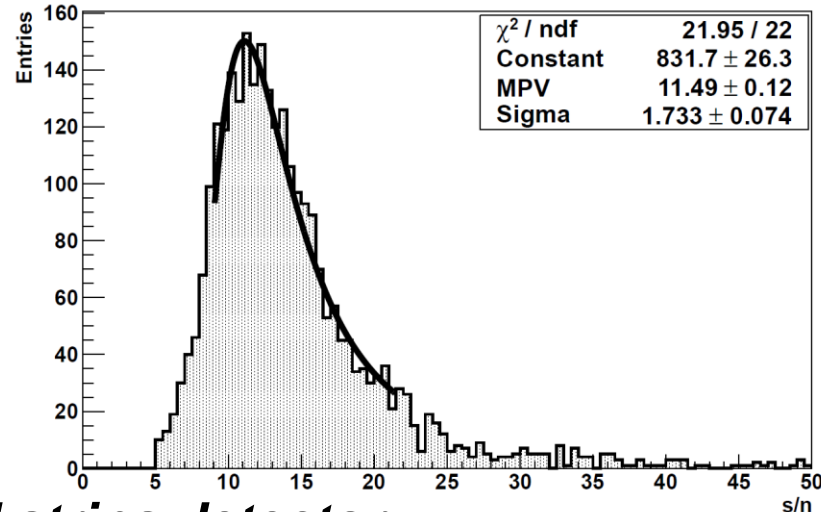
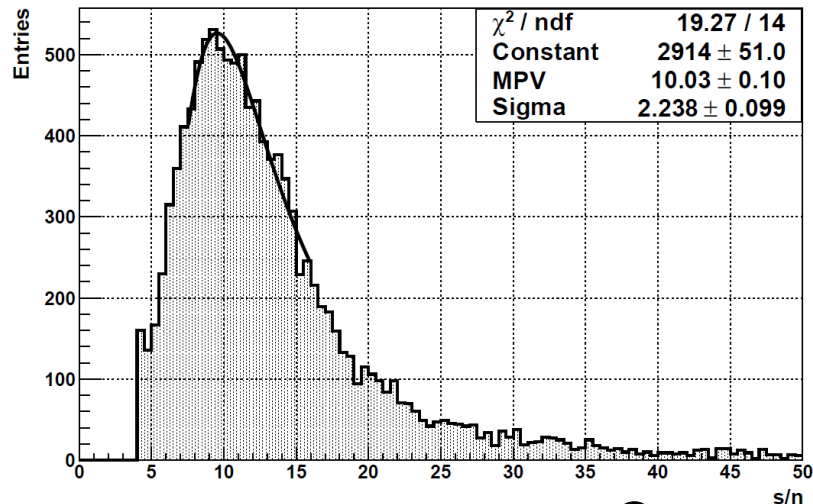
# s/n test beam vs s/n radioactive

source

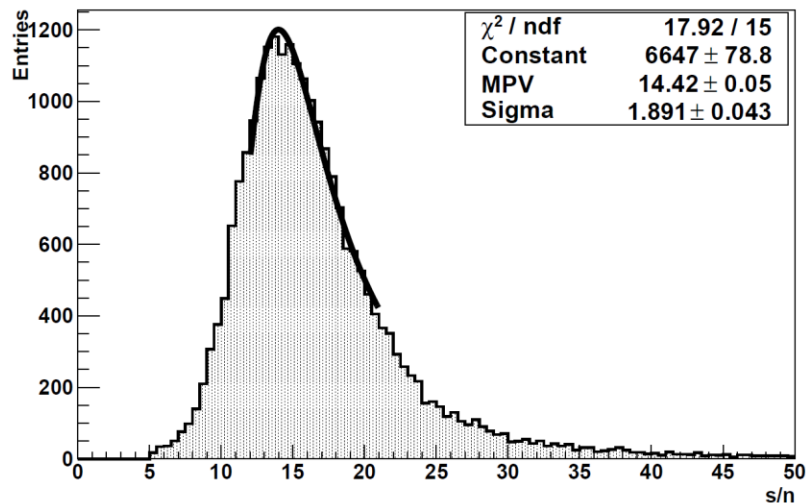
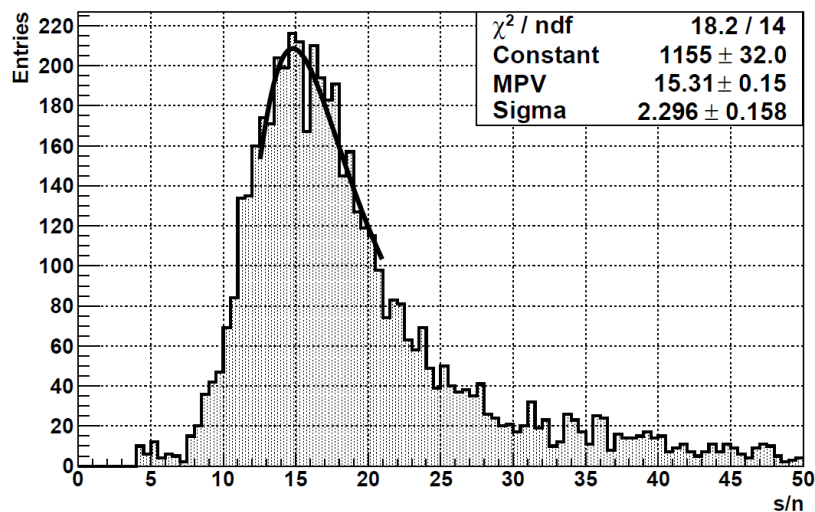


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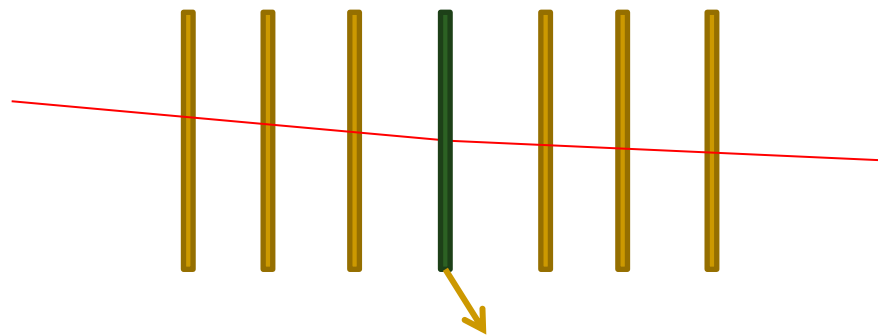
## *Resistive strips detector*



## *Conventional strips detector*

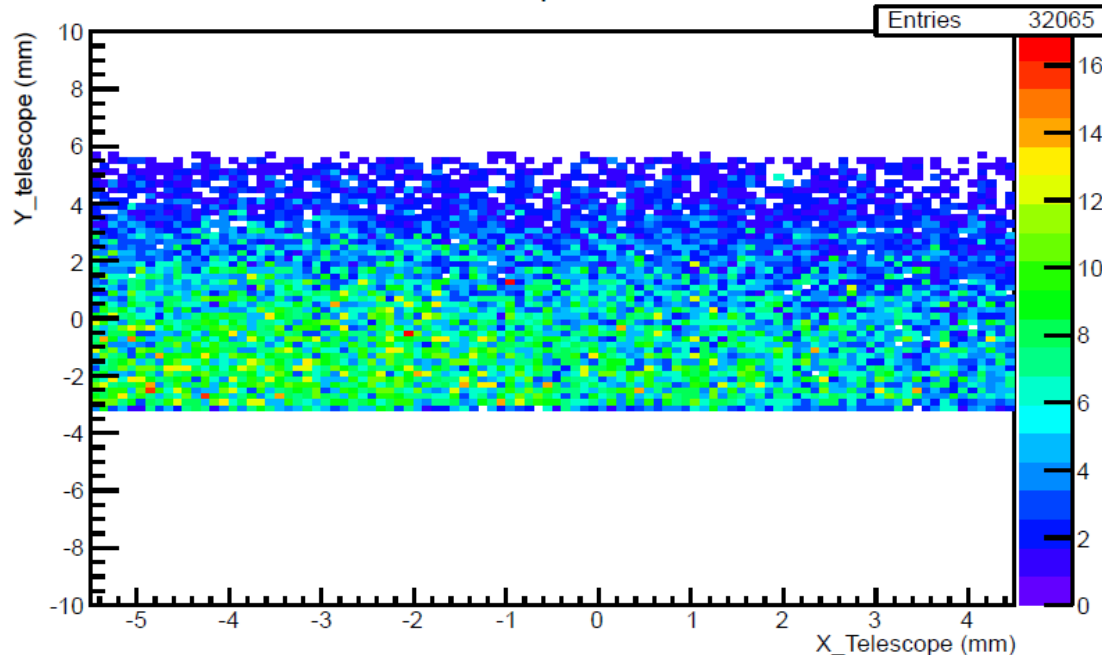


# Tracking (Telescopio)

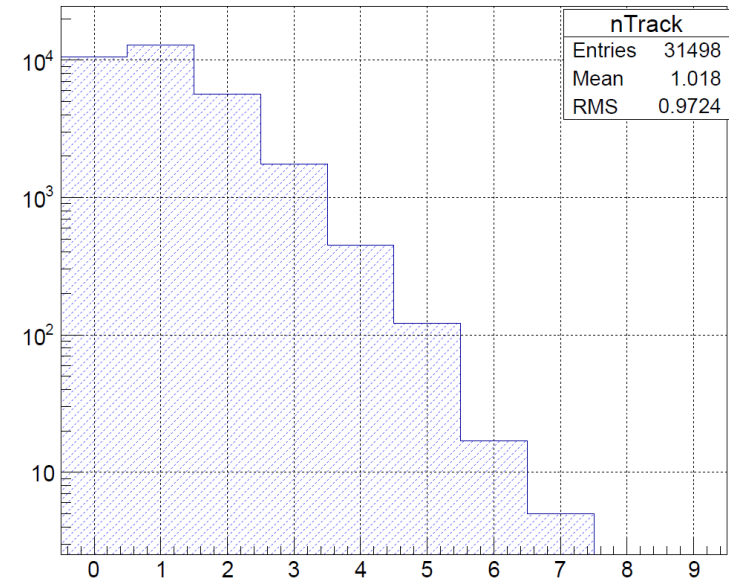


*Proyección plano DUT*

Telescope tracks



Number of reconstructed tracks in an event



*Distribución del número de trazas  
Totales por evento del telescopio  
en el plano del DUT*

*Trazas del telescopio proyectadas  
en el plano del DUT*

# Tracking (PolyA)



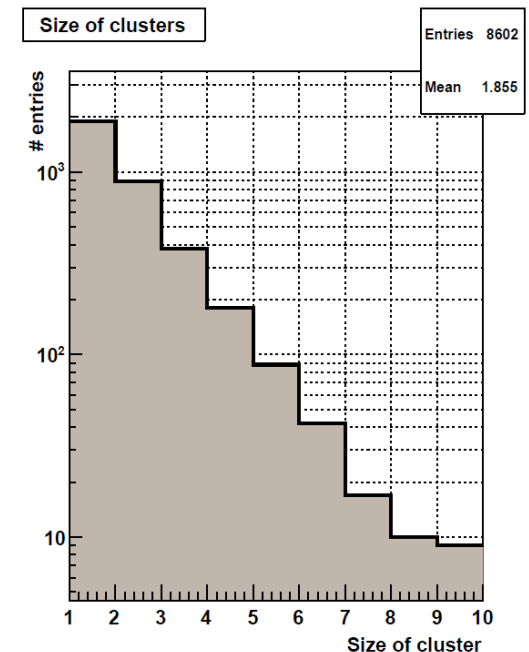
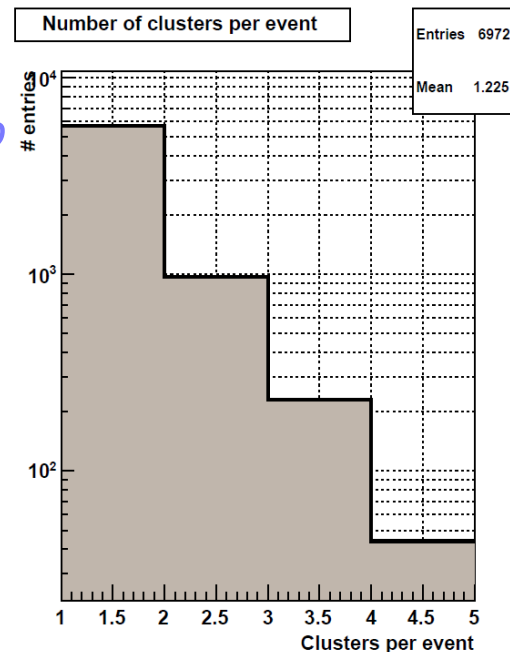
*Distribución del número de clusters*

*Detectados en el DUT:*

*Corte de 4 y 2 sigmas*

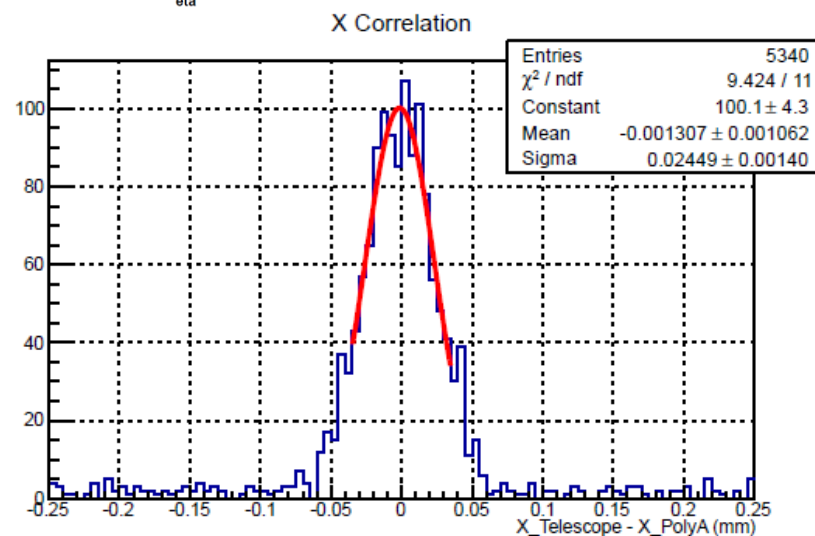
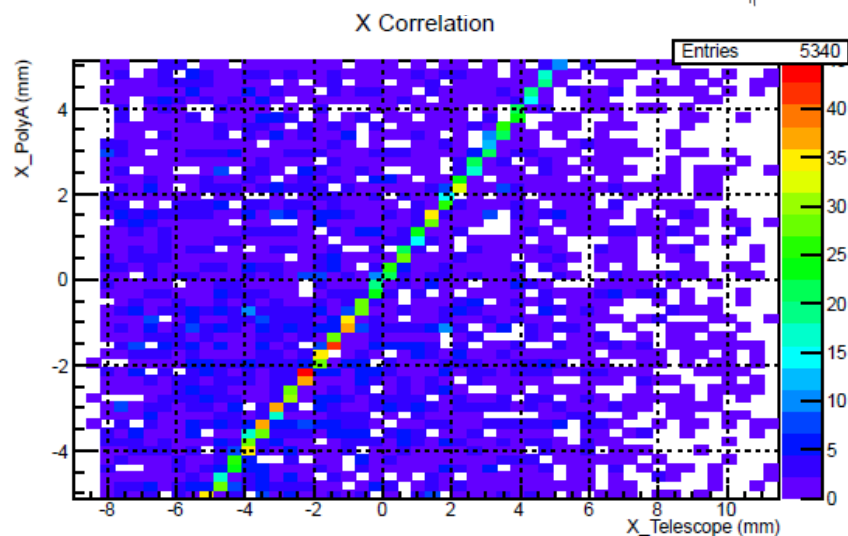
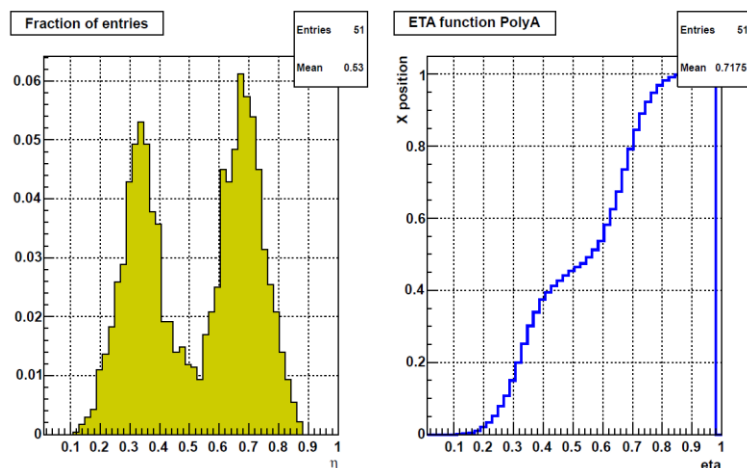
*No hay corte en tiempo 0-100 ns*

*Con un corte de 20-40 ns (selecciono el pico), no varían las resoluciones.*





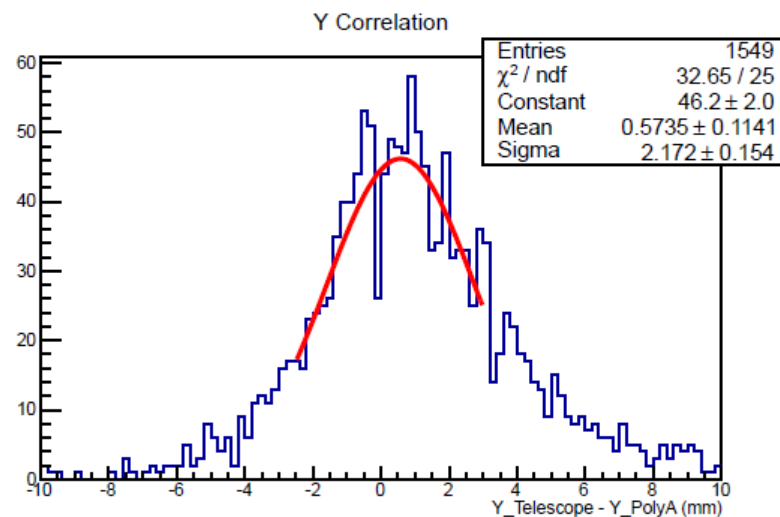
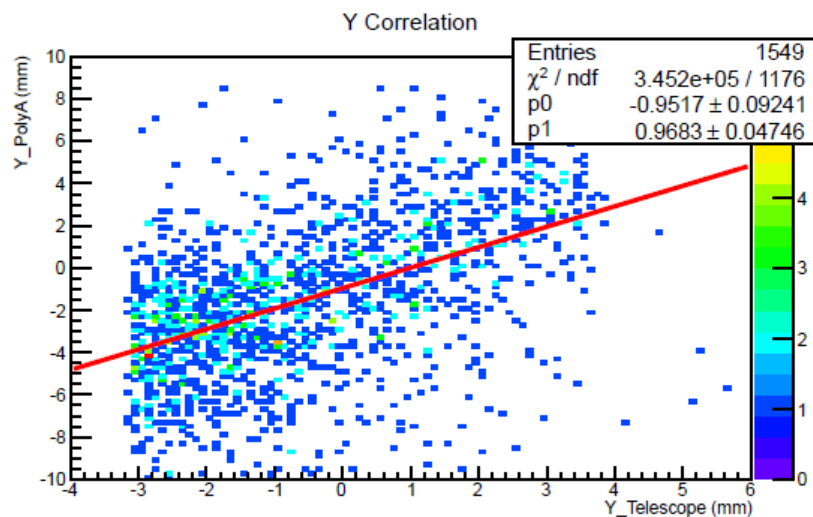
# X Resolution (transversal)



# Y resolution (logitudinal)



*Se usan sólo los clusters que machean previamente el la posición transversal,  
Se toma un corte de 5 sigmas (0.025 mm).*



- In terms of position resolution the sensors behaves as predicted. Is it enough ?
- No result on efficiency due to problems with the timing sensor and wrong sensor biasing.

# SEGMENTED P-TYPE SENSORS WITH CHARGE AMPLIFICATION



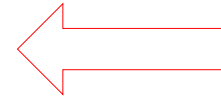
# Charge Multiplication- pixel detectors



We are starting the fabrication of new p-type pixel detectors with enhanced multiplication effect in the n-type electrodes, very low collection times and with no cross-talk.

Three different approaches:

1. Thin p-type epitaxial substrates
2. Low gain avalanche detectors
3. 3D with enhanced electric field.



Two projects funded by CERN RD50 collaboration to work on these technologies.

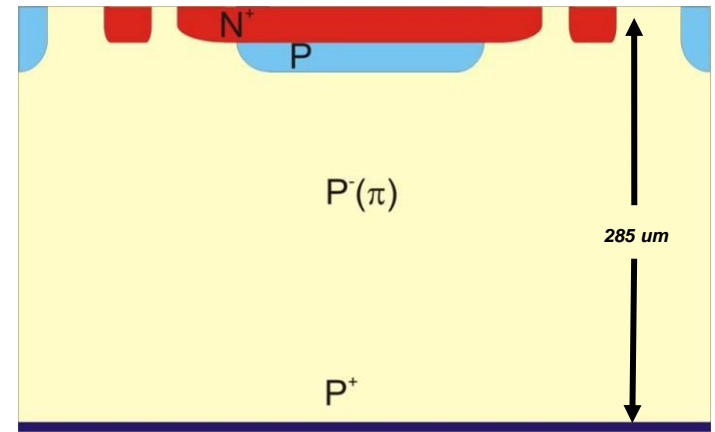
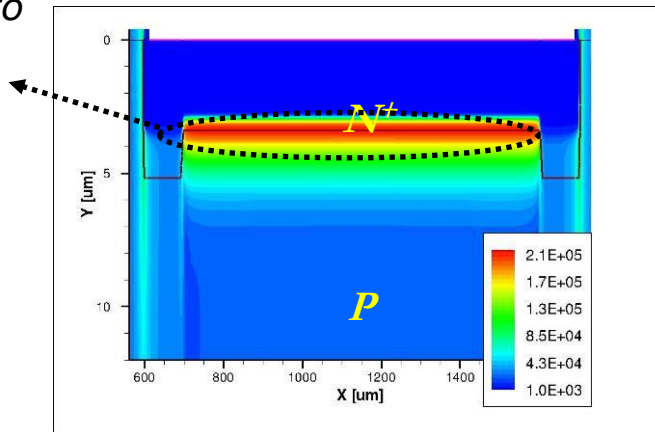
<http://rd50.web.cern.ch/rd50/>

# Low gain avalanche detectors (LGAD)

Implating an  $n^{++}/p^{+}/p^{-}$  junction along the centre of the electrodes. Under reverse bias conditions, a high electric field region is created at this localised region, which can lead to a multiplication mechanism (impact ionization).

***Advantages = Thinning while keeping same S/N as standard detectors.***

*High Electric Field region leading to multiplication*



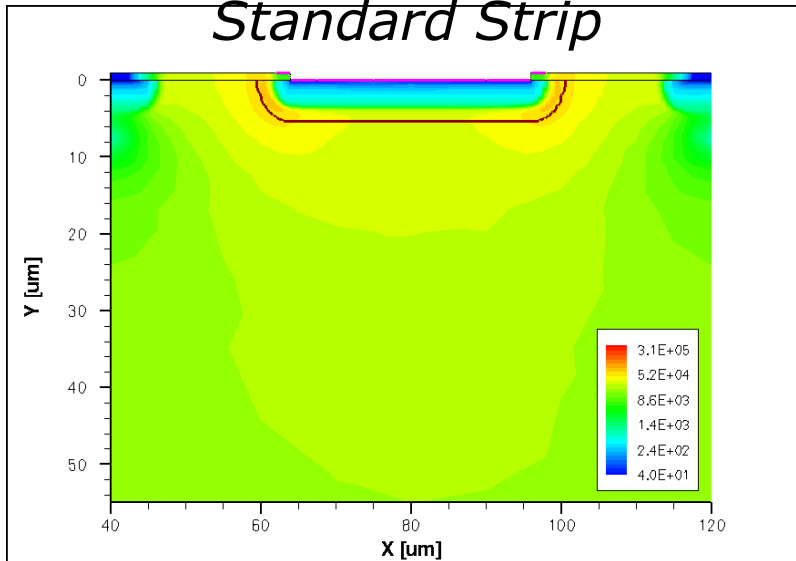
*P. Fernandez et al, "Simulation of new p-type strip detectors with trench to enhance the charge multiplication effect in the n-type electrodes", Nuclear Instruments and Methods in Physics Research A 658(2011) 98–102.*



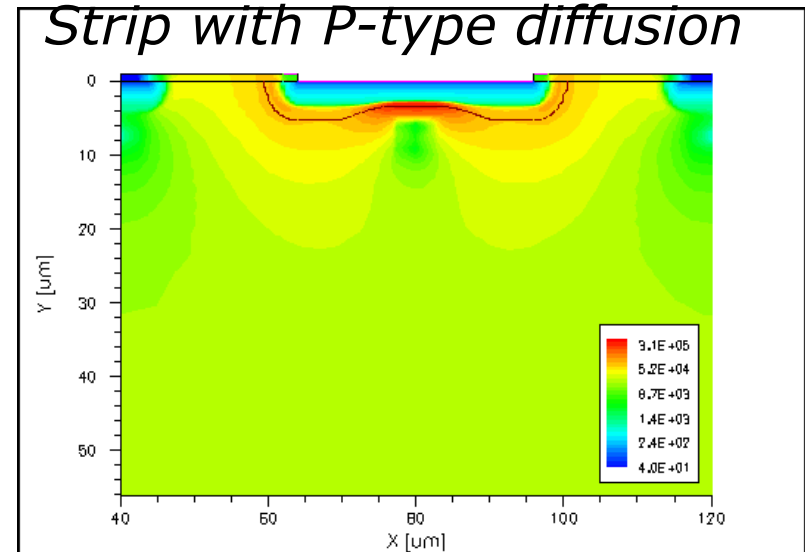
# Simulation of the Electric Field

- To obtain the manufacture parameters (doping profiles)

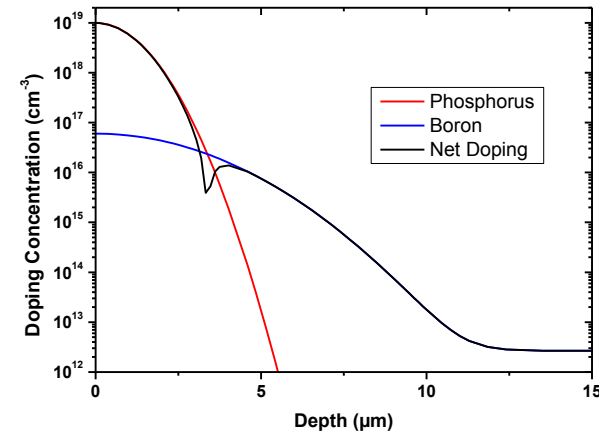
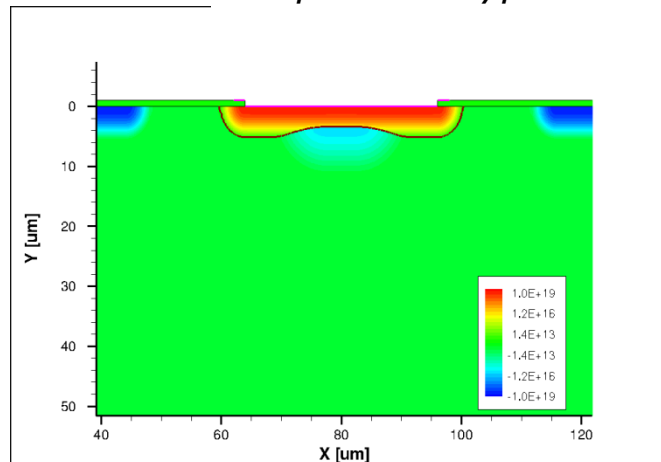
*Standard Strip*



*Strip with P-type diffusion*



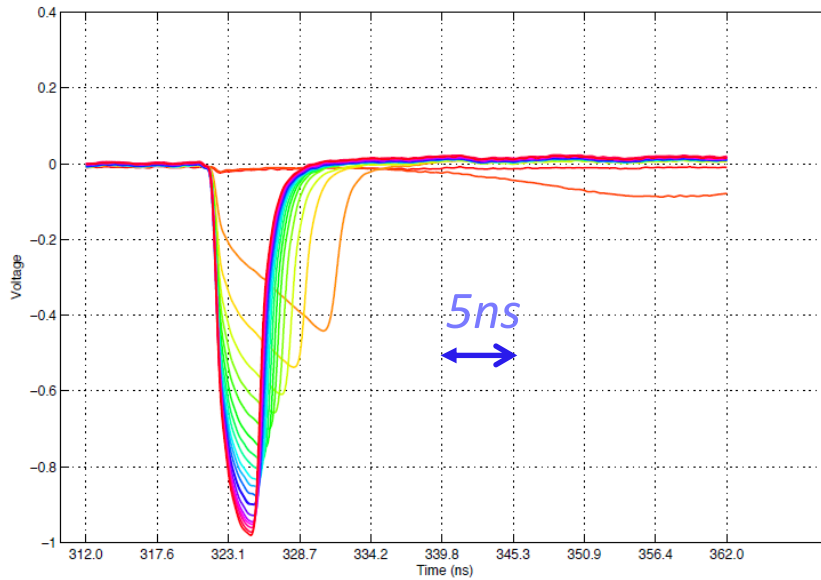
*Strip with P-type diffusion: 2D and 1D doping profiles*



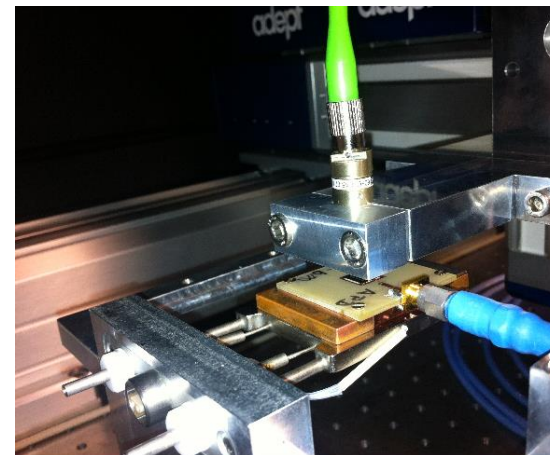
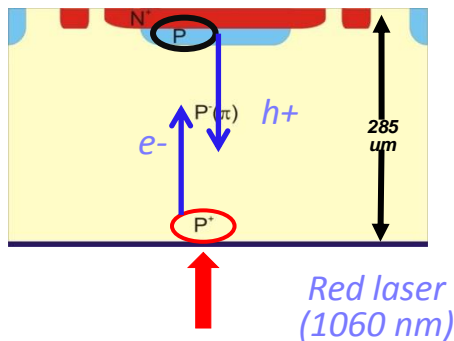
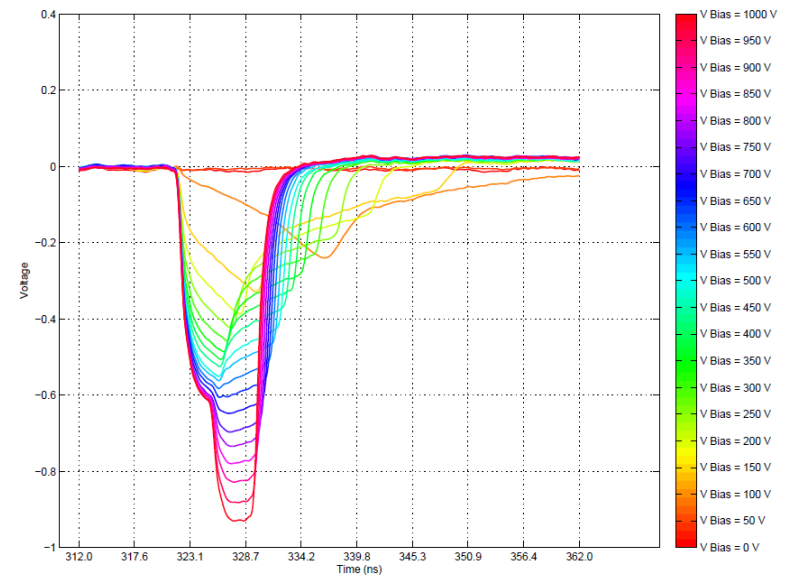
# Red laser TCT characterization

*Bottom injection*

*Standard diode n on p*



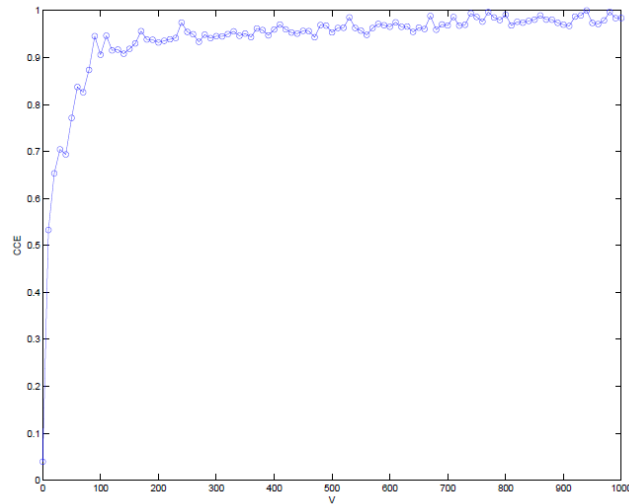
*P-type diffusion diode*



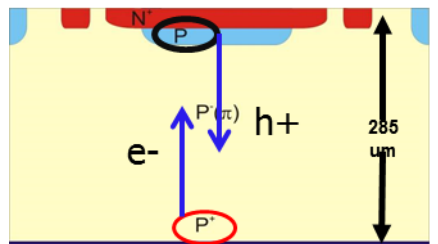
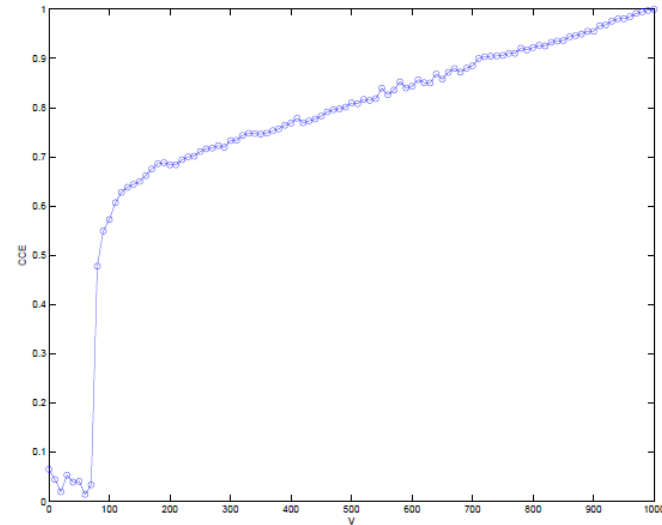
# Red laser TCT characterization

## Charge collection efficiency

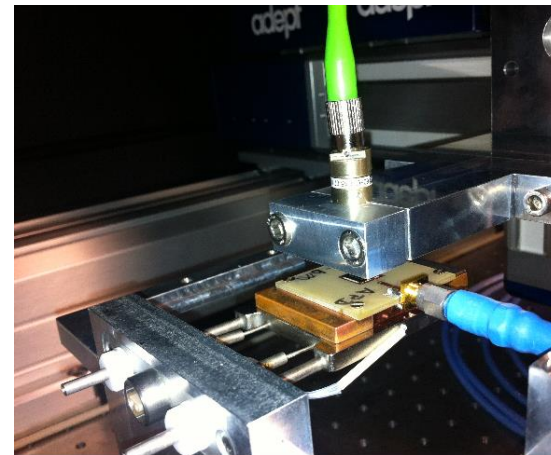
Standard diode



P-type diffusion diode



Red laser  
(1060 nm)



# GRACIAS !

